

M37753FFCFP M37753FFCHP

SINGLE-CHIP 16-BIT CMOS MICROCOMPUTER FLASH MEMORY VERSION

DESCRIPTION

The M37753FFCFP and the M37753FFCHP are single-chip microcomputers designed with high-performance CMOS silicon gate technology, including the internal flash memory. These are housed in 80-pin plastic molded QFP.

These microcomputers have a CPU and a bus interface unit. The CPU is a 16-bit parallel processor that can also be switched to perform 8-bit parallel processing, and the bus interface unit enhances the memory access efficiency to execute instructions fast.

In addition to the 7700 Family basic instructions, the M37753FFCFP and the M37753FFCHP have 6 special instructions which contain instructions for signed multiplication/division; these added instructions improve the servo arithmetic performance to control hard disk drives and so on.

These microcomputers also include the flash memory, RAM, multiple-function timers, motor control function, serial I/O, A-D converter, D-A converter, and so on.

The internal flash memory can be programed and erased by using a PROM programmer or by control of the central processing unit (CPU). Therefore, these microcomputers can change the program easily even after they are mounted on the board.

DISTINCTIVE FEATURES

<Microcomputer mode>

APPLICATION

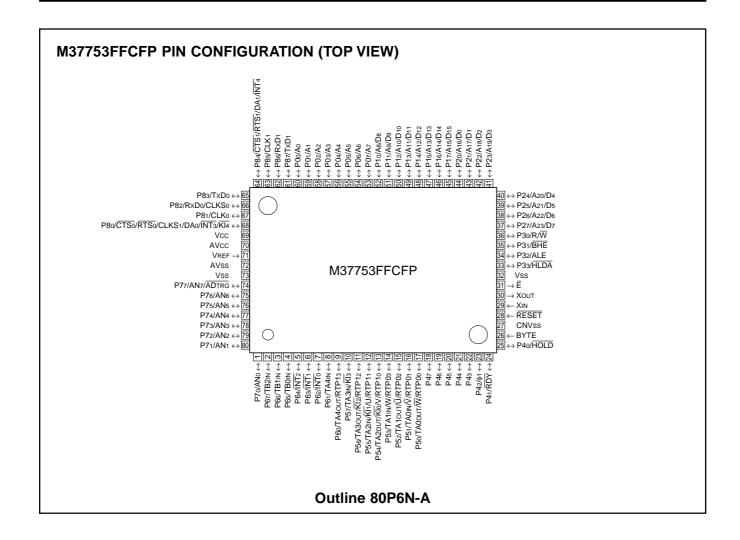
Control devices for personal computer peripheral equipment such as CD-ROM drives, hard disk drives, high density FDD, printers Control devices for office equipment such as copiers and facsimiles Control devices for industrial equipment such as communication and measuring instruments

Control devices for equipment required for motor control such as inverter air conditioner and general purpose inverter





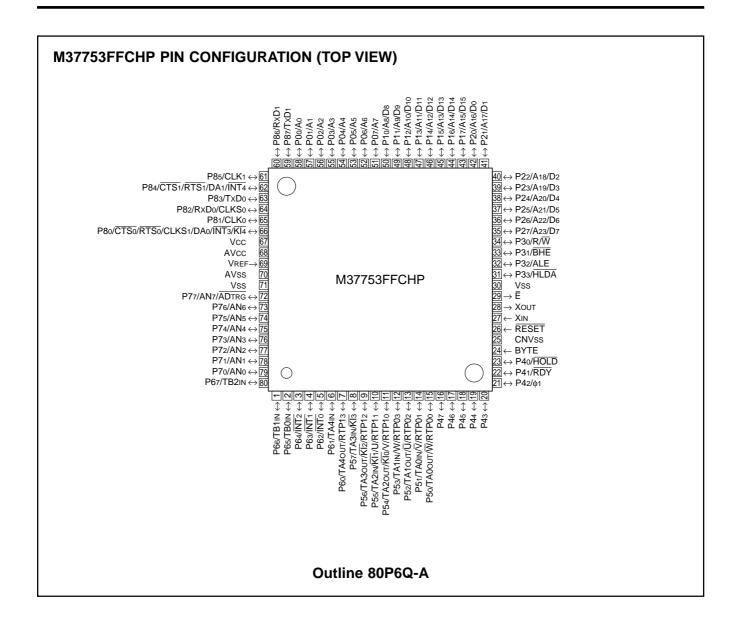








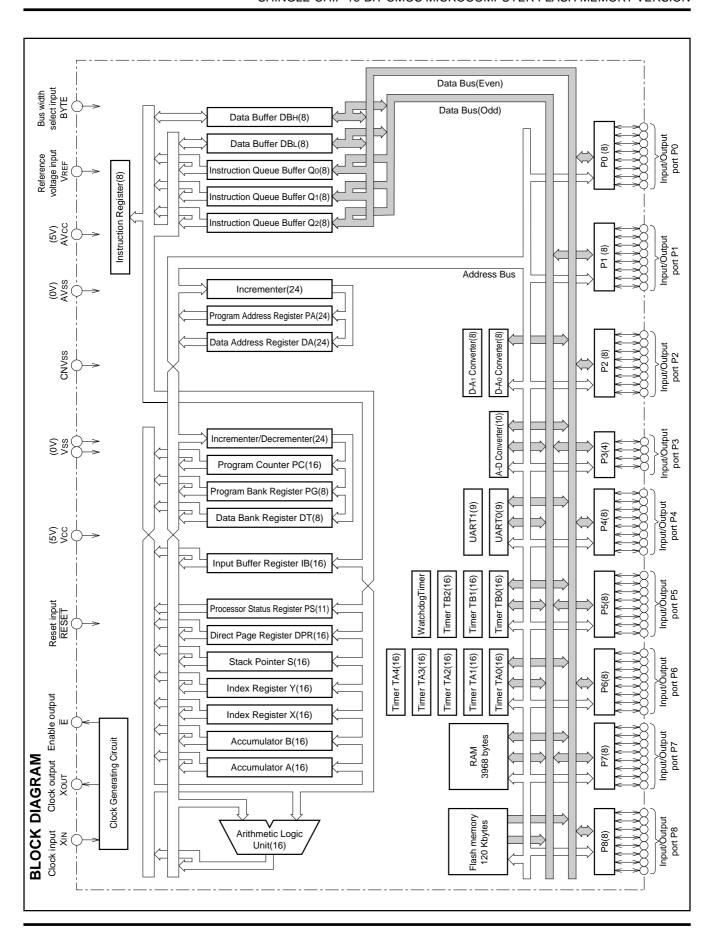


















FUNCTIONS (Microcomputer mode)

F	Parameter	Functions		
Number of basic machine instru	ıctions	109 (103 basic instructions of 7700 Family + 6 special instructions)		
Instruction execution time		100 ns (the fastest instruction at external clock 40 MHz frequency)		
Mamanyaira	Flash memory	120 Kbytes		
Memory size	RAM	3968 bytes		
Innut/Outnut norto	P0-P2, P4-P8	8-bit × 8		
Input/Output ports	P3	4-bit × 1		
Multiple-function timers	TA0, TA1, TA2, TA3, TA4	16-bit × 5		
Multiple-fullction timers	TB0, TB1, TB2	16-bit × 3		
Serial I/O		(UART or clock synchronous serial I/O) × 2		
A-D converter		10-bit × 1(8 channels)		
D-A converter		8-bit × 2		
Watchdog timer		12-bit × 1		
Dead-time timer		8 -bit \times 3		
Interrupts		5 external types, 16 internal types (Each interrupt can be set to priority levels 0 – 7.)		
Clock generating circuit		Built-in (externally connected to a ceramic resonator or quartz crystal resonato		
Supply voltage		5 V±10 %		
Power dissipation		125 mW (at external clock 40 MHz frequency)		
la mark/Outrout also marks mistic	Input/Output withstand voltage	5 V		
Input/Output characteristic	Output current	5 mA		
Memory expansion		Maximum 16 Mbytes		
Operating temperature range		−20 to 85 °C		
Device structure		CMOS high-performance silicon gate process		
Package		80-pin plastic molded QFP		

FUNCTIONS (Flash memory mode)

	Parameter	Functions		
Supply voltage		5 V ± 10 %		
Program/Erase voltage		12 V ± 5 %		
Flash memory mode		3 modes		
		(parallel I/O, serial I/O, CPU reprogramming)		
	Parallel I/O mode	Programming in unit of byte/120 Kbytes		
Programming method	Serial I/O mode	Programming in unit of byte/120 Kbytes		
	CPU reprogramming mode	Programming in unit of byte/112 Kbytes		
	Parallel I/O mode	Batch erasing/120 Kbytes		
.	Serial I/O mode	Batch erasing/120 Kbytes		
Erasing method	CPU reprogramming mode	Batch erasing/112 Kbytes or 2-division-block erasing		
	Cr o reprogramming mode	2-division-block erasing: 56-Kbyte area to be erased is selectable.		
Program/Erase control met	hod	Program/Erase control by software command		
	Parallel I/O mode	7 commands		
Command number	Serial IO mode	7 commands		
	CPU reprogramming mode	7 commands		
Number of times for Progra	ım/Erase	100		





M37753FFCFP M37753FFCHP

SHINGLE-CHIP 16-BIT CMOS MICROCOMPUTER FLASH MEMORY VERSION

PIN DESCRIPTION (MICROCOMPUTER MODE)

Pin	Name	Input/ Output	Functions
Vcc, Vss	Power supply		Supply 5 V±10 % to Vcc and 0 V to Vss.
CNVss	CNVss input	Input	This pin controls the processor mode. Connect to Vss for single-chip mode or memory expansion mode. Connect to Vcc for microprocessor mode.
RESET	Reset input	Input	This is reset input pin. The microcomputer is reset when supplying "L" level to this pin.
XIN	Clock input	Input	These are I/O pins of internal clock generating circuit. Connect a ceramic or quartz-crystal resonator between XIN and XOUT. When an external clock is used, the clock
Xout	Clock output	Output	source should be connected to the XIN pin and the XOUT pin should be left open.
Ē	Enable output	Output	Data or instruction read, data write are performed when output from this pin is "L".
BYTE (Note)	Bus width select input	Input	This pin determines whether the external data bus is 8-bit width or 16-bit width for memory expansion mode or microprocessor mode. The width is 16 bits when "L" signal inputs and 8 bits when "H" signal inputs.
AVCC, AVSS	Analog supply input		Power supply for the A-D converter and the D-A converter. Connect AVcc to Vcc and AVss to Vss externally.
VREF	Reference voltage input	Input	This is reference voltage input pin for the A-D converter and the D-A converter.
P00-P07	I/O port P0	I/O	In single-chip mode, port P0 is an 8-bit I/O port. This port has an I/O direction register and each pin can be programmed for input or output. These ports are in the input mode when reset. Address (A0–A7) is output in memory expansion mode or microprocessor mode.
P10-P17	I/O port P1	I/O	In single-chip mode, these pins have the same functions as port P0. When the BYTE pin is set to "L" in memory expansion mode or microprocessor mode and external data bus is 16-bit width, high-order data (D8–D15) is input or output if $\overline{\mathbb{E}}$ output is "L" and an address (A8–A15) is output if $\overline{\mathbb{E}}$ output is "H". When the BYTE pin is set to "H" and an external data bus is 8-bit width, only address (A8–A15) is output.
P20-P27	I/O port P2	I/O	In single-chip mode, these pins have the same functions as port P0. In memory expansion mode or microprocessor mode, low-order data (D0–D7) is input or output when \overline{E} output is "L" and an address (A16–A23) is output when \overline{E} output is "H".
P30-P33	I/O port P3	I/O	In single-chip mode, these pins have the same functions as port <u>P0. In memory expansion mode or microprocessor mode</u> , R/W, BHE, ALE, and HLDA signals are output.
P40-P47	I/O port P4	I/O	In single-chip mode, these pins have the same functions as port P0. In memory expansion mode or microprocessor mode, P40, P41, and P42 become $\overline{\text{HOLD}}$ and $\overline{\text{RDY}}$ input pins, and clock ϕ_1 output pin respectively. Functions of other pins are the same as in single-chip mode. In memory expansion mode, P42 can be programmed as I/O port.
P50-P57	I/O port P5	I/O	In addition to having the same functions as port P0 in single-chip mode, these pins also function as I/O pins for timer A0, timer A1, timer A2, timer A3, output pins for motor drive waveform, and input pins for key input interrupt.
P60-P67	I/O port P6	I/O	In addition to having the same functions as port P0 in single-chip mode, these pins also function as the I/O pin for timer A4, input pins for external interrupt input INT0, INT1, and INT2, and input pins for timer B0, timer B1, and timer B2, and output pin for motor drive wave form.
P70-P77	I/O port P7	I/O	In addition to having the same functions as port P0 in single-chip mode, these pins also function as input pins for A-D converter.
P80-P87	I/O port P8	I/O	In addition to having the same functions as port P0 in single-chip mode, these pins also function as I/O pins for UART0, UART1, output pins for D-A converter, and input pins for INT3, INT4.

Note: It is impossible to change the input level of the BYTE pin in each bus cycle. In other words, bus width cannot be switched dynamically. Fix the input level of the BYTE pin to "H" or "L" according to the bus width used.







PIN DESCRIPTION (FLASH MEMORY PARALLEL I/O MODE)

Pin	Name	Input /Output	Functions
Vcc, Vss	Power supply	_	Supply 5 V ± 10 % to Vcc and 0 V to Vss.
CNVss	VPP input	Input	Connect to 5 V ± 10 % in read-only mode, connect to 12 V ± 5 % in read/write mode.
BYTE	Bus width select input	Input	Connect to Vss.
RESET	Reset input	Input	Connect to Vss.
XIN	Clock input	Input	Connect a ceramic resonator between XIN and XOUT.
Хоит	Clock output	Output	
Ē	Enable output	Output	Keep it open.
AVcc, AVss	Analog supply input	_	Connect AVCC to VCC and AVss to Vss.
VREF	Reference voltage input	Input	Connect to Vss.
P00-P07	Address input (A0-A7)	Input	Port P0 functions as 8-bit address input (A0–A7).
P10-P17	Address input (A8-A15)	Input	Port P1 functions as 8-bit address input (A8–A15).
P20-P27	Data I/O (D0-D7)	I/O	Function as 8-bit data's I/O pins (D0–D7).
P30-P33	Input port P3	Input	Connect to Vss.
P40-P47	Input port P4	Input	Keep P42 open. Connect P40, P41, P43–P47 to Vss.
P50-P57	Control signal input	Input	P50, P51 and P52 function as the WE, OE and CE input pins respectively. P54 functions as the A16 input pin. Connect P53 to Vcc. Connect P55, P56 and P57 to Vss.
P60-P67	Input port P6	Input	Connect to Vss.
P70-P77	Input port P7	Input	Connect to Vss.
P80-P87	Input port P8	Input	Connect to Vss.







PIN DESCRIPTION (FLASH MEMORY SERIAL I/O MODE)

Pin	Name	Input /Output	Functions
Vcc, Vss	Power supply	_	Supply 5 V ± 10 % to Vcc and 0 V to Vss.
CNVss	VPP input	Input	Connect to 12 V ± 5 %.
BYTE	Bus width select input	Input	Connect to Vss or Vcc.
RESET	Reset input	Input	Connect to Vss.
XIN	Clock input	Input	Connect a ceramic resonator between XIN and XOUT.
Xout	Clock output	Output	
Ē	Enable output	Output	"H" is output.
AVcc, AVss	Analog supply input	_	Connect AVcc to Vcc and AVss to Vss.
VREF	Reference voltage input	Input	Input an arbitrary level between the range of Vss and Vcc.
P00-P07	Input port P0	Input	Input "H" or "L", or keep them open.
P10-P17	Input port P1	Input	Input "H" or "L", or keep them open.
P20-P27	Input port P2	Input	Input "H" or "L", or keep them open.
P30-P33	Input port P3	Input	Input "H" or "L", or keep them open.
P40–P43, P47	Input port P4	Input	Input "H" or "L" to P40, P41, P43, P47, or keep them open. Keep P42 open.
P44	BUSY output	Output	This pin is for BUSY signal output.
P45	SDA I/O	I/O	This pin is for serial data I/O.
P46	SCLK input	Input	This pin is for serial clock input.
P50, P52–P57	Input port P5	Input	Input "H" or "L", or keep them open.
P51	Control signal input	Input	OE input pin
P60-P67	Input port P6	Input	Input "H" or "L", or keep them open.
P70-P77	Input port P7	Input	Input "H" or "L", or keep them open.
P80-P87	Input port P8	Input	Input "H" or "L", or keep them open.





BASIC FUNCTION BLOCKS

The M37753FFCFP and the M37753FFCHP have the same functions as the M37753M8C-XXXGP and the M37753M8C-XXXHP except for the following.

Therefore, refer to the section on the M37753M8C-XXXGP and the M37753M8C-XXXHP.

- (1) Flash memory is included instead of ROM.
- (2) The memory size is different.
- (3) The memory area modification function is different.
- (4) Part of the peripheral devices control registers is different. (Flash memory control register, flash command register, and bits
 - 3, 4 of particular function select register 0 are added.)

MEMORY

The memory map is shown in Figure 1.

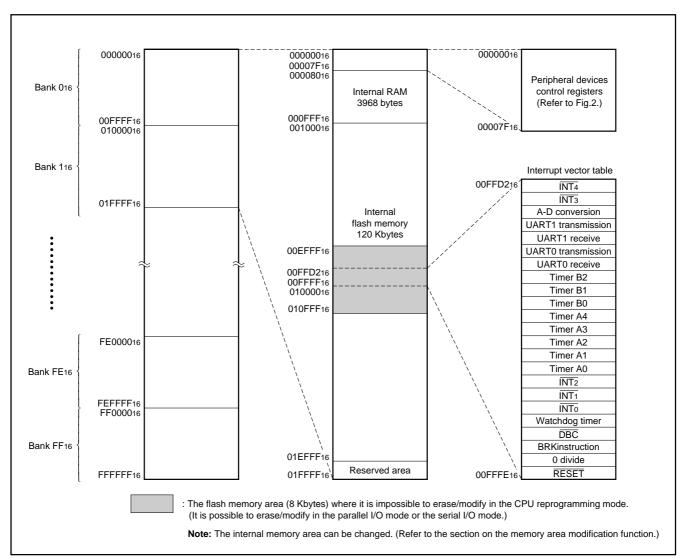


Fig. 1 Memory map







ddress (Hexa	decimal notation)	Address (Hexa	decimal notation)
000000	decimal notation)	000040	Count start register
000001		000040	Court start register
000002	Port P0 register	000042	One-shot start register
000003	Port P1 register	000043	
000004	Port P0 direction register	000044	Up-down register
000005	Port P1 direction register	000045	Timer A write flag
000006	Port P2 register	000046	Timer A0 register
000007 000008	Port P3 register	000047 000048	
000008	Port P2 direction register Port P3 direction register	000048	Timer A1 register
000003 00000A	Port P4 register	000049 00004A	
00000B	Port P5 register	00004B	Timer A2 register
00000C	Port P4 direction register	00004C	Timer A2 register
00000D	Port P5 direction register	00004D	Timer A3 register
00000E	Port P6 register	00004E	Timer A4 register
00000F	Port P7 register	00004F	·····c································
000010	Port P6 direction register	000050	Timer B0 register
000011	Port P7 direction register Port P8 register	000051	
000012 000013	i oit i o iegistei	000052 000053	Timer B1 register
000013	Port P8 direction register	000053	T. Do
000017	2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	000055	Timer B2 register
000016		000056	Timer A0 mode register
000017		000057	Timer A1 mode register
000018		000058	Timer A2 mode register
000019		000059	Timer A3 mode register
00001A	Waveform output mode register	00005A	Timer A4 mode register
00001B	Dead-time timer	00005B	Timer B0 mode register
00001C 00001D	Pulse output data register 1 Pulse output data register 0	00005C 00005D	Timer B1 mode register Timer B2 mode register
00001D 00001E	A-D control register 0	00005D 00005E	Processor mode register 0
00001E	A-D control register 1	00005E	Processor mode register 1
000020		000060	Watchdog timer register
000021	A-D register 0	000061	Watchdog timer frequency select regsiter
000022	A-D register 1	000062	
000023	A-D register 1	000063	
000024	A-D register 2	000064	Comparator function select register
000025	<u> </u>	000065	Flash command register
000026 000027	A-D register 3	000066 000067	Comparator result register Flash memory control register
000027		000067	D-A register 0
000029	A-D register 4	000069	2 / Trogistor o
00002A	A D register 5	00006A	D-A register 1
00002B	A-D register 5	00006B	
00002C	A-D register 6	00006C	Particular function select register 0
00002D	7. D Togistor 0	00006D	Particular function select register 1
00002E	A-D register 7	00006E	INT4 interrupt control register
00002F	•	00006F	INT3 interrupt control register
000030 000031	UART0 transmit/receive mode register UART0 baud rate register	000070 000071	A-D interrupt control register UART0 trasmit interrupt control register
000031		000071	UARTO trasmit interrupt control register
000032	UART0 transmit buffer register	000072	UART1 trasmit interrupt control register
000033	UART0 transmit/receive control register 0	000073	UART1 receive interrupt control register
000035	UART0 transmit/receive control register 1	000075	Timer A0 interrupt control register
000036	UART0 receive buffer register	000076	Timer A1 interrupt control register
000037	The state of the s	000077	Timer A2 interrupt control register
000038	UART1 transmit/receive mode register	000078	Timer A3 interrupt control register
000039	UART1 baud rate register	000079	Timer A4 interrupt control register
00003A	UART1 transmit buffer register	00007A	Timer B0 interrupt control register
00003B		00007B	Timer B1 interrupt control register
00003C 00003D	UART1 transmit/receive control register 0 UART1 transmit/receive control register 1	00007C 00007D	Timer B2 interrupt control register INTo interrupt control register
00003D 00003E		00007D 00007E	INTo interrupt control register
00003E	UART1 receive buffer register	00007E	INT2 interrupt control register

Fig. 2 Location of peripheral devices and interrupt control registers







	Address			Address	
Port P0 direction register	(0416)	0016	Watchdog timer (6016)	FFF16
Port P1 direction register	(0516)	0016	Watchdog timer frequency select register	(6116)	XXXXXX o c
Port P2 direction register	(0816) 0	0000	Comparator function select register	(6416)	0016
Port P3 direction register	(0916)	0000	Comparator result register	(6616)	0016
Port P4 direction register	(0C ₁₆)	0016	Flash memory control register	(6716)	\times 0 0 0 0 0 0 0
Port P5 direction register	(0D ₁₆)	0016	D-A register 0	(6816)	0016
Port P6 direction register	(1016)	0016	D-A register 1	(6A ₁₆)	0016
Port P7 direction register	(1116)	0016	Particular function select register 0	(6C ₁₆)	0016
Port P8 direction register	(1416)	0016	Particular function select register 1	(6D ₁₆)	0016
Waveform output mode register	(1A ₁₆)	0016	INT4 interrupt control register	(6E ₁₆)	00000
Pulse output data register 1	(1C ₁₆)	0016	INT3 interrupt control register	(6F ₁₆)	0 0 0 0 0 0 0
Pulse output data register 0	(1D ₁₆) 0 0	0 0 0 0 0	A-D interrupt control register	(7016)	? 0 0 0
A-D control register 0	(1E ₁₆) 0 0	0 0 0 ? ? ?	UART 0 transmit interrupt control register	(7116)	0000
A-D control register 1	(1F ₁₆) 0 0	0 0 0 0 1 1	UART 0 receive interrupt control register	(7216)	
UART 0 transmit/receive mode register	(3016)	0016	UART 1 transmit interrupt control register	(7316)	0000
UART 1 transmit/receive mode register	(3816)	0016	UART 1 receive interrupt control register	(7416)	
UART 0 transmit/receive control register 0	(3416) 0	0 1 0 0 0	Timer A0 interrupt control register	(7516)	0000
UART 1 transmit/receive control register 0	(3C ₁₆) 0	0 1 0 0 0	Timer A1 interrupt control register	(7616)	0000
UART 0 transmit/receive control register 1	(3516) 0 0	0 0 0 0 1 0	Timer A2 interrupt control register	(7716)	XXX0000
UART 1 transmit/receive control register 1	(3D ₁₆) 0 0	0 0 0 0 1 0	Timer A3 interrupt control register	(7816)	XXX0000
Count start register	(4016)	0016	Timer A4 interrupt control register	(7916)	0000
One-shot start register	(4216)	00000	Timer B0 interrupt control register	(7A ₁₆)	XXX0000
Up-down register	(4416) 0 0	0 0 0 0 0 0	Timer B1 interrupt control register	(7B ₁₆)	0000
Timer A write flag	(4516)	000	Timer B2 interrupt control register	(7C ₁₆)	
Timer A0 mode register	(5616)	0016	INTo interrupt control register	(7D ₁₆)	00000
Timer A1 mode register	(5716)	0016	INT1 interrupt control register	(7E ₁₆)	00000
Timer A2 mode register	(5816)	0016	INT2 interrupt control register	(7F ₁₆)	00000
Timer A3 mode register	(5916)	0016	Processor status register PS	0 0 0	? ? 0 0 0 1 ? 3
Timer A4 mode register	(5A ₁₆)	0016	Program bank register PG		0016
Timer B0 mode register	(5B ₁₆) 0 0	1 0 0 0 0	Program counter PCH		Contents of FFFF16
Timer B1 mode register	(5C ₁₆) 0 0	1 0 0 0 0	Program counter PCL		Contents of FFFE16
Timer B2 mode register	(5D ₁₆) 0 0	1 0 0 0 0	Direct page register DPR		000016
Processor mode register 0	(5E ₁₆) 0 0	0 0 0 0 1 0	Data bank register DT		0016
Processor mode register 1	(5F ₁₆)	0016	Contents of other registers and R/itiallzed by software.	AM are not	initialized and must be in

Fig. 3 Microcomputer internal registers status after reset





MEMORY AREA MODIFICATION FUNCTION

For the M37753FFCFP and the M37753FFCHP, the internal memory's size and address area can be changed by setting bits 2, 3, 4 (memory allocation select bits) of the particular function select register 0 (see figure 5). Figure 4 shows the memory map when changing the internal memory area.

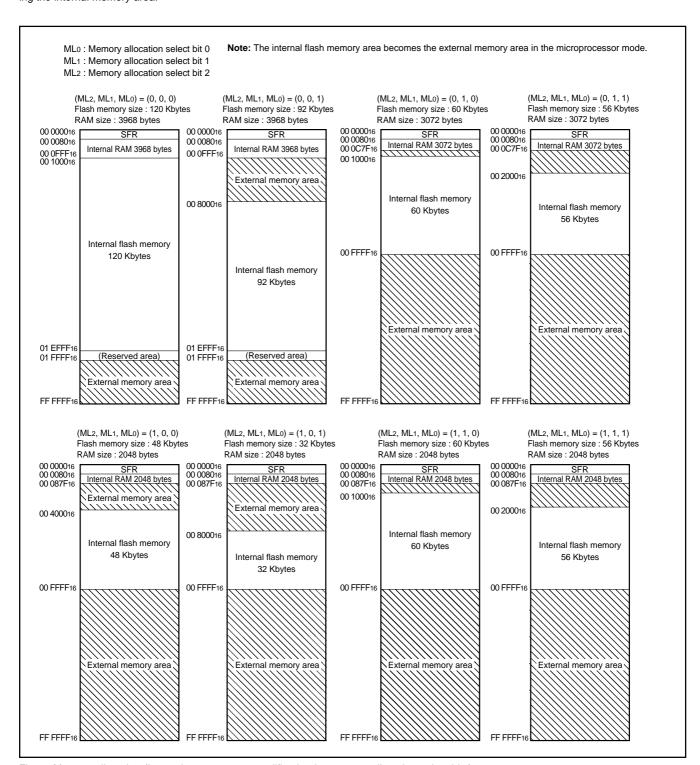


Fig. 4 Memory allocation (Internal memory area modification by memory allocation select bits)







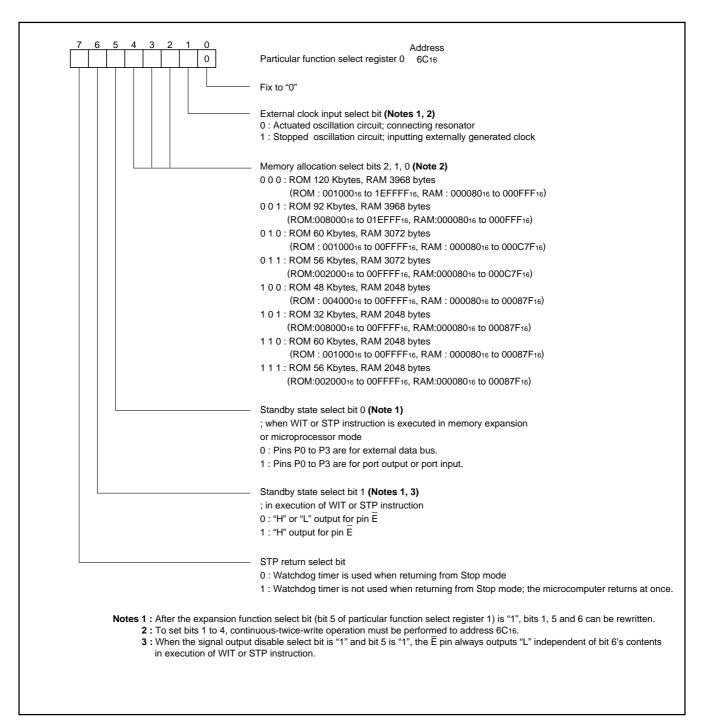


Fig. 5 Particular function select register 0 bit configuration





FLASH MEMORY MODE

The M37753FFCFP and the M37753FFCHP have the flash memory mode in addition to the normal operation mode (microcomputer mode). The user can use this mode to perform read, program, and erase operations for the internal flash memory.

The M37753FFCFP and the M37753FFCHP have three modes the user can choose: the parallel input/output and serial input/output mode, where the flash memory is handled by using the external programmer, and the CPU reprogramming mode, where the flash memory is handled by the central processing unit (CPU). The following explains these modes.

Flash memory mode 1 (parallel I/O mode)

The parallel I/O mode can be selected by connecting wires as shown in Figures 6, 7 and supplying power to the Vcc and VPP pins. In this mode, the M37753FFCFP and the M37753FFCHP operate as an equivalent of MITSUBISHI's CMOS flash memory M5M28F101. However, because the M37753FFCFP and the M37753FFCHP's internal memory has a capacity of 120 Kbytes, programming is available for addresses 0100016 to 1EFFF16, and make sure that the data in addresses 0000016 to 00FFF16 and addresses 1F00016 to 1FFFF16 are FF16. Note also that the M37753FFCFP and the M37753FFCHP do not contain a facility to read out a device identification code by applying a high voltage to address input (A9). Be careful not to erratically set program conditions when using a general-purpose PROM programmer.

Table 1 shows the pin assignments when operating in the parallel input/output mode.

Table 1. Pin assignments of M37753FFCFP and M37753FFCHP when operating in the parallel input/output mode

	M37753FFCFP/CHP	M5M28F101
Vcc	Vcc	Vcc
VPP	CNVss	VPP
Vss	Vss	Vss
Address input	Ports P0, P1, P54	A0-A16
Data I/O	Port P2	D0-D7
CE	P52	CE
OE	P51	ŌĒ
WE	P50	WE

Functional outline (Parallel input/output mode)

In the parallel input/output mode, the M37753FFCFP and the M37753FFCHP allow the user to choose an operation mode between the read-only mode and the read/write mode (software command control mode) depending on the voltage applied to the VPP pin. When VPP = VPPL, the read-only mode is selected, and the user can choose one of three states (e.g., read, output disable, or standby) depending on inputs to the $\overline{\text{CE}}$, $\overline{\text{OE}}$, and $\overline{\text{WE}}$ pins. When VPP = VPPH, the read/write mode is selected, and the user can choose one of four states (e.g., read, output disable, standby, or write) depending on inputs to the $\overline{\text{CE}}$, $\overline{\text{OE}}$, and $\overline{\text{WE}}$ pins. Table 2 shows assignment states of control input and each state.

Read

The microcomputer enters the read state by driving the \overline{CE} , and \overline{OE} pins low and the \overline{WE} pin high; and the contents of memory corresponding to the address to be input to address input pins (A0–A16). are output to the data input/output pins (D0–D7).

Output disable

The microcomputer enters the output disable state by driving the $\overline{\text{CE}}$ pin low and the $\overline{\text{WE}}$ and $\overline{\text{OE}}$ pins high; and the data input/output pins enter the floating state.

Standby

The microcomputer enters the standby state by driving the $\overline{\text{CE}}$ pin high. The M37753FFCFP and the M37753FFCHP are placed in a power-down state consuming only a minimal supply current. At this time, the data input/output pins enter the floating state.

Write

The microcomputer enters the write state by driving the VPP pin high (VPP = VPPH) and then the \overline{WE} pin low when the \overline{CE} pin is low and the \overline{OE} pin is high. In this state, software commands can be input from the data input/output pins, and the user can choose program or erase operation depending on the contents of this software command.

Table 2. Assignment sates of control input and each state

Mode	Pin State	CE	ŌĒ	WE	VPP	Data I/O
	Read	VIL	VIL	ViH	VPPL	Output
Read-only	Output disable	VIL	VIH	ViH	VPPL	Floating
	Standby	VIH	×	×	VPPL	Floating
	Read	VIL	VIL	ViH	VPPH	Output
Read/Write	Output disable	VIL	VIH	ViH	VPPH	Floating
	Standby	ViH	×	×	VPPH	Floating
	Write	VIL	VIH	VIL	VPPH	Input

Note: \times can be VIL or VIH.





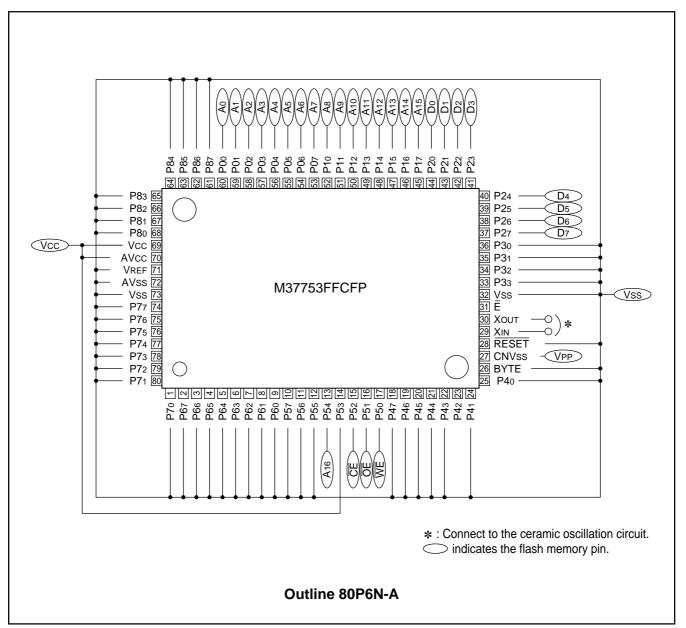


Fig. 6 Pin connection of M37753FFCFP when operating in parallel input/output mode



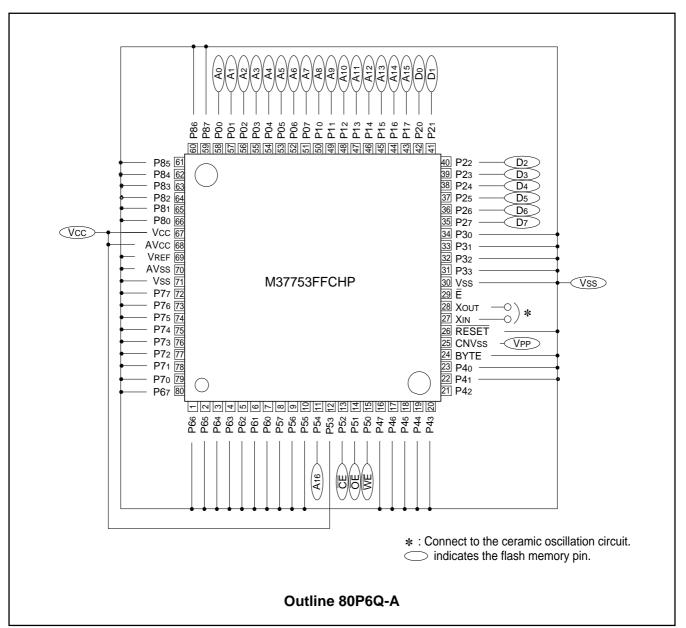


Fig. 7 Pin connection of M37753FFCHP when operating in parallel input/output mode







Read-only mode

The microcomputer enters the read-only mode by applying VPPL to the VPP pin. In this mode, the user can input the address of a memory location to be read and the control signals at the timing shown in Figure 8, and the M37753FFCFP and the M37753FFCHP will output the contents of the user's specified address from data I/O pin to the external. In this mode, the user cannot perform any operation other than read.

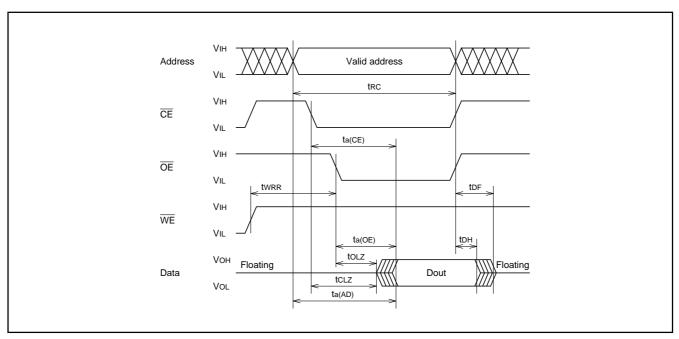


Fig. 8 Read timing

Read/Write mode

The microcomputer enters the read/write mode by applying VPPH to the VPP pin. In this mode, the user must first input a software command to choose the operation (e. g., read, program, or erase) to be performed on the flash memory (this is called the first cycle), and then input the information necessary for execution of the command (e.g., address and data) and control signals (this is called the second cycle). When this is done, the M37753FFCFP and the M37753FFCHP execute the specified operation.

Table 3 shows the software commands and the input/output information in the first and the second cycles. The input address is latched internally at the falling edge of the $\overline{\text{WE}}$ input; software commands and other input data are latched internally at the rising edge of the $\overline{\text{WE}}$ input.

The following explains each software command. Refer to Figures 9 to 11 for details about the signal input/output timings.

Table 3. Software command (Parallel input/output mode)

Cymbol	First	cycle	Second cycle		
Symbol	Address input	Data input	Address input	Data I/O	
Read	×	0016	Read address	Read data (Output)	
Program	×	4016	Program address	Program data (Input)	
Program verify	×	C016	×	Verify data (Output)	
Erase	×	2016	×	2016 (Input)	
Erase verify	Verify address	A016	×	Verify data (Output)	
Reset	×	FF16	×	FF16 (Input)	
Device identification	×	9016	ADI	DDI (Output)	

Note: ADI = Device identification address : manufacturer's code 0000016, device code 0000116

DDI = Device identification data : manufacturer's code 1C16, device code D016

X can be VIL or VIH.







Read command

The microcomputer enters the read mode by inputting command code "0016" in the first cycle. The command code is latched into the internal command latch at the rising edge of the $\overline{\text{WE}}$ input. When the address of a memory location to be read is input in the second cycle, with control signals input at the timing shown in Figure 9, the M37753FFCFP and the M37753FFCHP output the contents of the specified address from the data I/O pins to the external.

The read mode is retained until any other command is latched into the command latch. Consequently, once the M37753FFCFP and the M37753FFCHP enter the read mode, the user can read out the successive memory contents simply by changing the input address and executing the second cycle only. Any command other than the read command must be input beginning from its command code over again each time the user execute it. The contents of the command latch immediately after power-on is 0016.

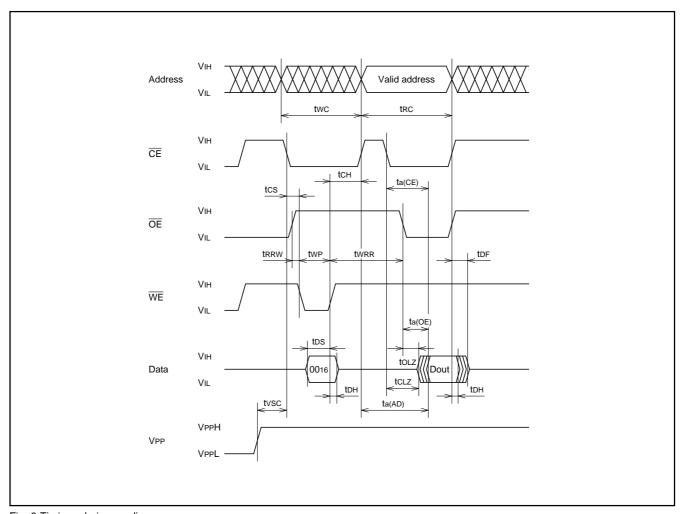


Fig. 9 Timings during reading





Program command

The microcomputer enters the program mode by inputting command code "4016" in the first cycle. The command code is latched into the internal command latch at the rising edge of the \overline{WE} input. When the address which indicates a program location and data are input in the second cycle, the M37753FFCPP and the M37753FFCHP internally latch the address at the falling edge of the \overline{WE} input and the data at the rising edge of the \overline{WE} input. The M37753FFCPP and the M37753FFCHP start programming at the rising edge of the \overline{WE} input in the second cycle and finishes programming within 10 μs as measured by its internal timer. Programming is performed in units of bytes.

Note: A programming operation is not completed by executing the program command once. Always be sure to execute a program verify command after executing the program command. When the failure is found in this verification, the user must repeatedly execute the program command until the pass. Refer to Figure 12 for the programming flowchart.

Program verify command

The microcomputer enters the program verify mode by inputting command code "C016" in the first cycle. This command is used to verify the programmed data after executing the program command. The command code is latched into the internal command latch at the rising edge of the $\overline{\text{WE}}$ input. When control signals are input in the second cycle at the timing shown in Figure 10, the M37753FFCFP and the M37753FFCHP output the programmed address's contents to the external. Since the address is internally latched when the program command is executed, there is no need to input it in the second cycle.

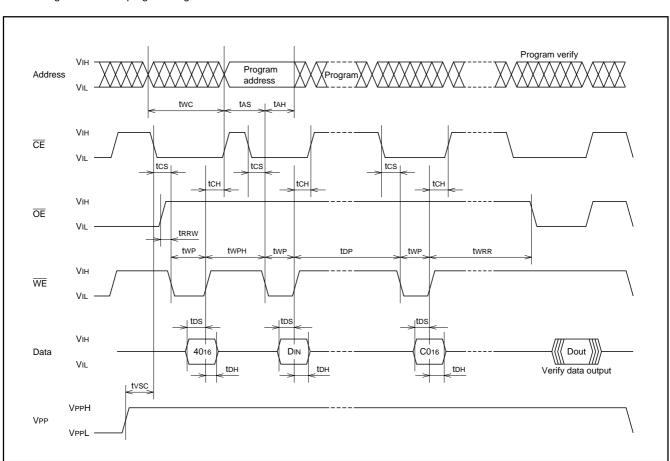


Fig. 10 Input/output timings during programming (Verify data is output at the same timing as for read.)







Erase command

The erase command is executed by inputting command code 2016 in the first cycle and command code 2016 again in the second cycle. The command code is latched into the internal command latch at the rising edges of the WE input in the first cycle and in the second cycle, respectively. The erase operation is initiated at the rising edge of the WE input in the second cycle, and the memory contents are collectively erased within 9.5 ms as measured by the internal timer. Note that data 0016 must be written to all memory locations before executing the erase command.

Note: An erase operation is not completed by executing the erase command once. Always be sure to execute an erase verify command after executing the erase command. When the failure is found in this verification, the user must repeatedly execute the erase command until the pass. Refer to Figure 12 for the erase flowchart.

Erase verify command

The user must verify the contents of all addresses after completing the erase command. The microcomputer enters the erase verify mode by inputting the verify address and command code A016 in the first cycle. The address is internally latched at the falling edge of the $\overline{\text{WE}}$ input, and the command code is internally latched at the rising edge of the $\overline{\text{WE}}$ input. When control signals are input in the second cycle at the timing shown in Figure 11, the M37753FFCFP and the M37753FFCHP output the contents of the specified address to the external.

Note: If any memory location where the contents have not been erased is found in the erase verify operation, execute the operation of "erase → erase verify" over again. In this case, however, the user does not need to write data 0016 to memory locations before erasing.

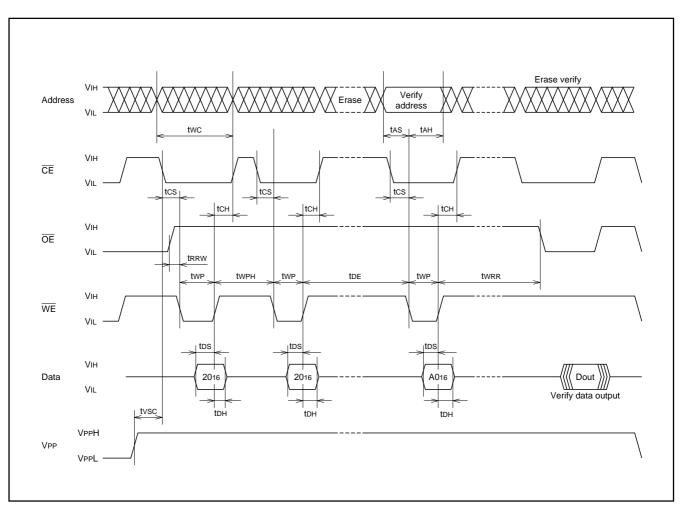
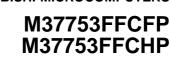


Fig. 11 Input/output timings during erasing (Verify data is output at the same timing as for read.)







Reset command

The reset command provides a means of stopping execution of the erase or program command safely. If the user inputs command code FF16 in the second cycle after inputting the erase or program command in the first cycle and again input command code FF16 in the third cycle, the erase or program command is disabled (i.e., reset), and the M37753FFCFP and the M37753FFCHP are placed in the read mode. If the reset command is executed, the contents of the memory does not change.

Device identification code command

By inputting command code 9016 in the first cycle, the user can read out the device identification code. The command code is latched into the internal command latch at the rising edge of the $\overline{\text{WE}}$ input. At this time, the user can read out manufacture's code 1C16 (i.e., MITSUBISHI) by inputting 000016 to the address input pins in the second cycle; the user can read out device code D016 (i. e., 1M-bit flash memory) by inputting 000116.

These command and data codes are input/output at the same timing as for read.







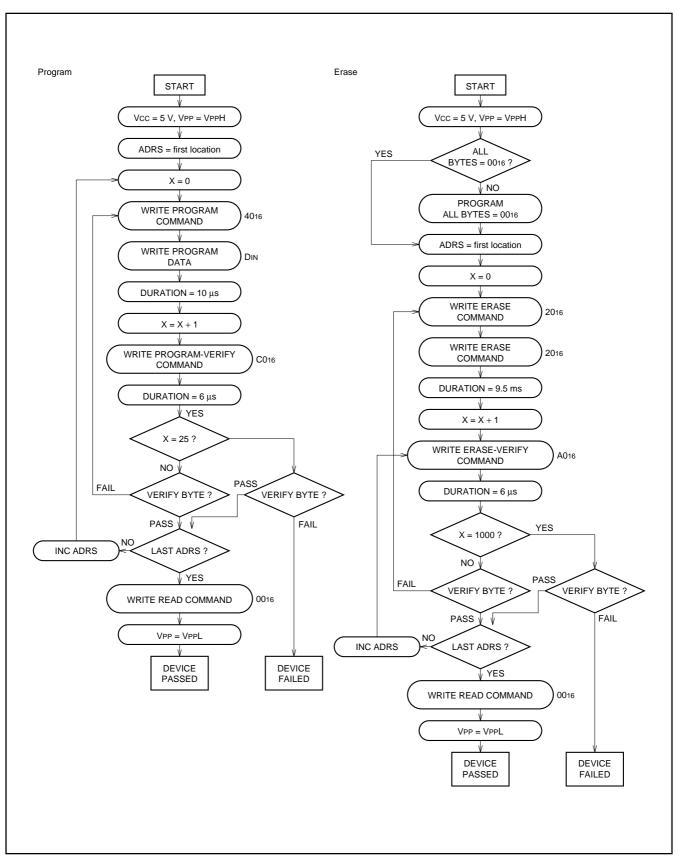


Fig. 12 Programming/Erasing algorithm flow chart







DC ELECTRICAL CHARACTERISTICS (Ta = 25 °C, Vcc = 5 V ± 10 %, unless otherwise noted)

Courada ad	Darameter	To at a smallting a		Limits		Unit
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	
ISB1		VCC = 5.5 V, $\overline{\text{CE}}$ = VIH			1	mA
ISB2	Vcc supply current (at standby)	$\frac{\text{VCC} = 5.5 \text{ V},}{\text{CE} = \text{VCC} \pm 0.2 \text{ V}}$			100	μΑ
ICC1	Vcc supply current (at read)	$VCC = 5.5 \text{ V}, \overline{CE} = VIL,$ tRC = 150 ns, IOUT = 0 mA			30	mA
ICC2	Vcc supply current (at program)	VPP = VPPH			30	mA
Іссз	Vcc supply current (at erase)	VPP = VPPH			30	mA
		0≤Vpp≤Vcc			10	μΑ
IPP1	VPP supply current (at read)	VCC <vpp≤vcc +="" 1.0="" td="" v<=""><td></td><td></td><td>100</td><td>μΑ</td></vpp≤vcc>			100	μΑ
		VPP = VPPH			100	μΑ
IPP2	VPP supply current (at program)	VPP = VPPH			30	mA
IPP3	VPP supply current (at erase)	VPP = VPPH			30	mA
VPPL	VPP supply voltage (read only)		Vcc		Vcc + 1.0	V
VPPH	VPP supply voltage (read/write)		11.4	12.0	12.6	V

Note: VIH, VIL, VOH, VOL, IIH, and IIL for the control input, address input, and data input/output pins conform to the standards for microcomputer modes (e.g., memory expansion and microprocessor modes).

AC ELECTRICAL CHARACTERISTICS (Ta = 25 °C, Vcc = 5 V ± 10 %, unless otherwise noted)

Read-only mode

Symbol	Parameter	Limits		Llait
		Min.	Max.	Unit
tRC	Read cycle time	150		ns
ta(AD)	Address access time		150	ns
ta(CE)	CE access time		150	ns
ta(OE)	OE access time		55	ns
tCLZ	Output enable time (after CE)	0		ns
tolz	Output enable time (after $\overline{\text{OE}}$)	0		ns
tDF	Output floating time (after OE)		35	ns
tDH	Output valid time (after CE, OE, address)	0		ns
twrr	Write recovery time (before read)	6		μs

Read/Write mode

Symbol	Parameter.	Limits		Unit
	Parameter		Max.	
twc	Write cycle time	150		ns
tAS	Address set up time	0		ns
tah	Address hold time	60		ns
tDS	Data setup time	50		ns
tDH	Data hold time	10		ns
twrr	Write recovery time (before read)	6		μs
trrw	Read recovery time (before write)	0		μs
tcs	CE setup time	20		ns
tCH	CE hold time	0		ns
tWP	Write pulse width	60		ns
tWPH	Write pulse waiting time	20		ns
tDP	Program time	10		μs
tDE	Erase time	9.5		ms
tvsc	VPP setup time	1		μs

Note: The read timing in the read/write mode is the same timing as in the read-only mode.







Flash memory mode 2 (serial I/O mode)

The M37753FFCFP and the M37753FFCHP have a function to serially input/output the software commands, addresses, and data required for operation on the internal flash memory (e. g., read, program, and erase) using only a few pins. This is called the serial I/ O (input/output) mode. This mode can be selected by driving the SDA (serial data input/output), SCLK (serial clock input), and $\overline{\text{OE}}$

pins high after connecting wires as shown in Figures 13, 14 and powering on the Vcc pin and then applying VPPH to the VPP pin.

In the serial I/O mode, the user can use seven types of software commands: bank (0, 1) select, read, program, program verify, auto erase, and error check.

Serial input/output is accomplished synchronously with the clock, beginning from the LSB (LSB first).

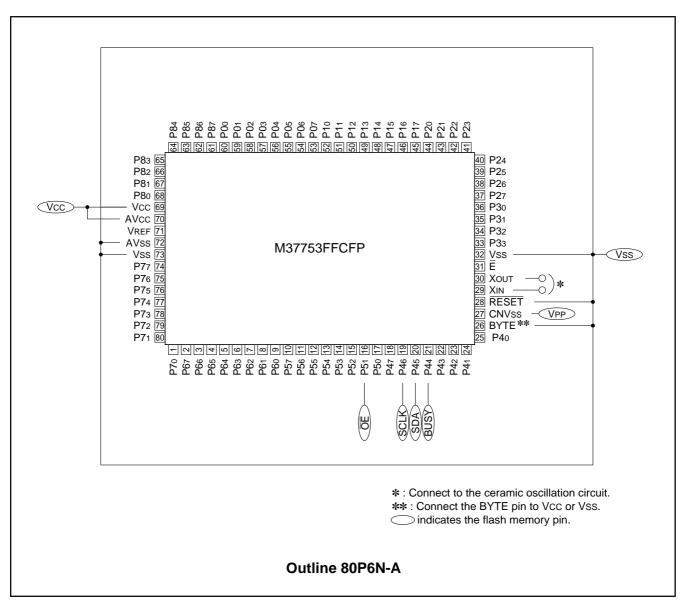


Fig. 13 Pin connection of M37753FFCFP when operating in serial I/O mode





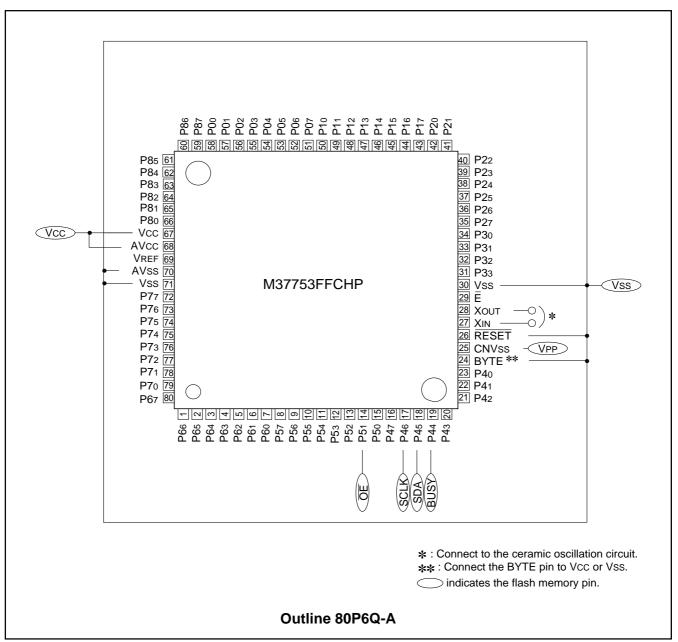


Fig. 14 Pin connection of M37753FFCHP when operating in serial I/O mode





Functional outline (Serial I/O mode)

In the serial I/O mode, data is transferred synchronously with the clock using serial input/output. The input data is read from the SDA pin into the internal circuit synchronously with the rising edge of the serial clock pulse; the output data is output from the SDA pin synchronously with the falling edge of the serial clock pulse. Data is

transferred in units of eight bits.

In the first transfer, the user inputs the command code. This is followed by address input and data input/output according to the contents of the command. Table 4 shows the software commands used in the serial I/O mode. The following explains each software command.

Table 4. Software command (Serial I/O mode)

Number of transfers	First command	Second	Third	Fourth	
Command	code input	Second	Tillia	T Guitii	
Bank 0 select	E016				
Bank 1 select	E116				
Read	0016	Read address L (Input)	Read address H (Input)	Read data (Output)	
Program	4016	Program address L (Input)	Program address H (Input)	Program data (Input)	
Program verify	C016	Verify data (Output)			
Auto erase	3016	3016 (Input)			
Error check	8016	Error code (Output)			

Bank select command

This is the command which specifies the bank of the flash memory, which is to be read/programmed, before executing the read command or the program command (and the program verify command). There are the bank 0 select command (command code "E016"), which selects bank 0 (addresses 0000016 to 0FFFF16), and the bank 1 select command (command code "E116"), which selects bank 1 (addresses 1000016 to 1FFFF16).

When any bank select command is input once, specified bank is

valid until the next bank select command is input. Accordingly, when the read command or the program command (and the program verify command) is executed to plural bytes in the same bank, if any bank select command is input first, it is unnecessary to input the bank select command again for the following bytes. When selecting the serial I/O mode (before bank command input), bank 0 is selected.

Note: Bank select command does not affect the auto erase command, that is to say, when executing the auto erase command, all flash memory is erased collectively regardless of specified bank.

And in the same way, the bank select command does not affect the error check command.

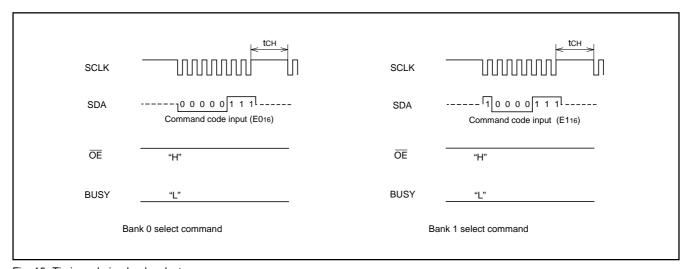


Fig. 15 Timings during bank select





M37753FFCFP M37753FFCHP

SHINGLE-CHIP 16-BIT CMOS MICROCOMPUTER FLASH MEMORY VERSION

Read command

Input command code 0016 in the first transfer. Proceed and input the low-order 8 bits and the high-order 8 bits of the address and pull the $\overline{\text{OE}}$ pin low. When this is done, the M37753FFCFP and the M37753FFCHP read out the contents of the specified address, and

then latch it into the internal data latch. When the \overline{OE} pin is released back high and serial clock is input to the SCLK pin, the read data that has been latched into the data latch is serially output from the SDA pin.

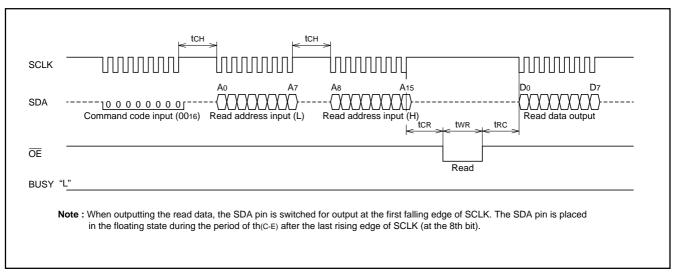


Fig. 16 Timings during reading





Program command

Input command code 4016 in the first transfer. Proceed and input the low-order 8 bits and the high-order 8 bits of the address and then program data. Programming is initiated at the last rising edge of the serial clock during program data transfer. The BUSY pin is driven high during program operation. Programming is completed within 10 μs as measured by the built-in timer, and the BUSY pin is pulled low.

Note: A programming operation is not completed by executing the program command once. Always be sure to execute a program verify command after executing the program command. In the case of failure in the verification, the user must repeatedly execute the program command until the pass in the verification. Refer to Figure 12 for the programming flowchart.

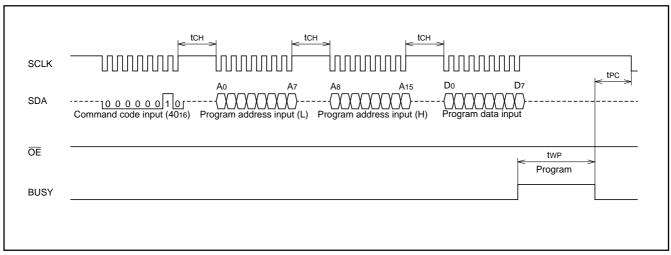


Fig. 17 Timings during programming

Program verify command

Input command code C016 in the first transfer. Proceed and drive the $\overline{\text{OE}}$ pin low. When this is done, the M37753FFCFP and the M37753FFCHP verify-read the programmed address's contents,

and then latch it into the internal data latch. When the $\overline{\text{OE}}$ pin is released back high and serial clock is input to the SCLK pin, the verify data that has been latched into the data latch is serially output from the SDA pin.

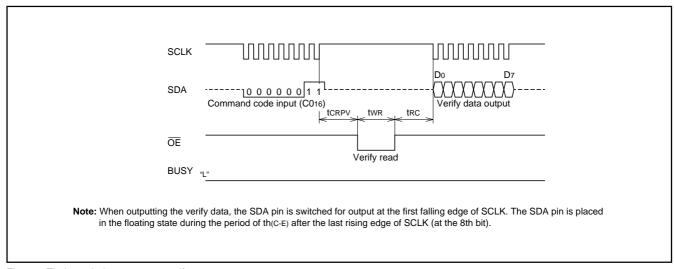


Fig. 18 Timings during program verify







Auto erase command

Input command code 3016 in the first transfer and command code 3016 again in the second transfer. When this is done, the M37753FFCFP and the M37753FFCHP execute an auto erase command. Auto erase is initiated at the last rising edge of the serial clock. The BUSY pin is driven high during the auto erase operation. Auto

erase is completed when all memory contents are erased, and the BUSY pin is pulled low.

Note: In the auto erase operation, the M37753FFCFP and the M37753FFCHP automatically repeat the erase and verify operations internally. Therefore, erase is completed by executing the command once.

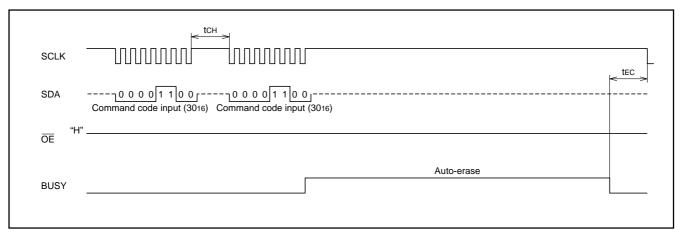


Fig. 19 Timings at auto-erasing

Error check command

Input command code 8016 in the first transfer, and the M37753FFCFP and the M37753FFCHP output error information from the SDA pin, beginning at the next falling edge of the serial clock. If the E0 of the 8-bit error information is 1, it indicates that a command error has occurred. A command error means that some invalid commands other than commands shown in Table 4 has been input.

When a command error occurs, the serial communication circuit sets the corresponding flag and stops functioning to avoid an erroneous programming or erase. When being placed in this state, the serial communication circuit does not accept the subsequent serial clock and data (even including an error check command). Therefore, if the

user wants to execute an error check command, temporarily drop the VPP pin input to the VPPL level to terminate the serial input/output mode. Then, place the M37753FFCFP and the M37753FFCHP into the serial I/O mode back again. The serial communication circuit is reset by this operation and is ready to accept commands. The error flag alone is not cleared by this operation, so the user can examine the serial communication circuit's error conditions before reset. This examination is done by the first execution of an error check command after the reset. The error flag is cleared when the user has executed the error check command. Because the error flag is undefined immediately after power-on, always be sure to execute the error check command.

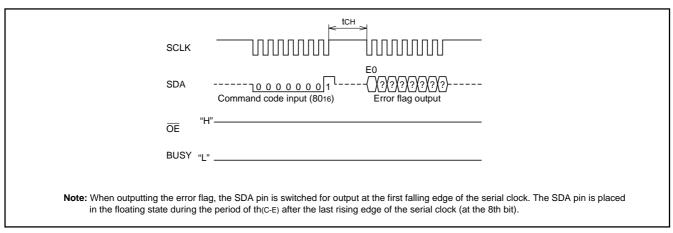


Fig. 20 Timings at error checking





DC ELECTRICAL CHARACTERISTICS (Ta = 25 °C, Vcc = 5 V ± 10 %, VPP = 12 V ± 5 %, unless otherwise noted) Icc, IPP-relevant standards during read, program, and erase are the same as in the parallel input/output mode. VIH, VIL, VOH, VOL, IIH, and IIL for the SCLK, SDA, BUSY, \overline{OE} pins conform to the microcomputer modes.

AC ELECTRICAL CHARACTERISTICS

(Ta = 25 °C, Vcc = 5 V \pm 10 %, VPP = 12 V \pm 5 %, f(XIN) = 40 MHz, unless otherwise noted)

Symbol	Parameter	Lin	Limits	
		Min.	Max.	Unit
tch	Serial transmission interval	400(Note 1)		ns
tCR	Read waiting time after transmission	400(Note 1)		ns
twr	Read pulse width	320(Note 2)		ns
tRC	Transfer waiting time after read	400(Note 1)		ns
tCRPV	Waiting time before program verify	6		μs
twp	Programming time		10	μs
tPC	Transfer waiting time after programming	400(Note 1)		ns
tEC	Transfer waiting time after erase	400(Note 1)		ns
tc(CK)	SCLK input cycle time	250		ns
tw(CKH)	SCLK high-level pulse width	100		ns
tw(CKL)	SCLK low-level pulse width	100		ns
tr(CK)	SCLK rise time	20		ns
tf(CK)	SCLK fall time	20		ns
td(C-Q)	SDA output delay time	0	90	ns
th(C-Q)	SDA output hold time	0		ns
th(C-E)	SDA output hold time (only the 8th bit)	120(Note 3)	200(Note 4)	ns
tsu(D-C)	SDA input set up time	30		ns
th(C-D)	SDA input hold time	90		ns

Notes 1: When f(XIN) = 25 MHz or less, calculate the minimum value according to formula 1.

Formula 1 : $\frac{1 \times 10}{f(XIN)} \times 10^9$

2: When f(XIN) = 25 MHz or less, calculate the minimum value according to formula 2.

Formula 2: $\frac{1 \times 8}{f(XIN)} \times 10^9$

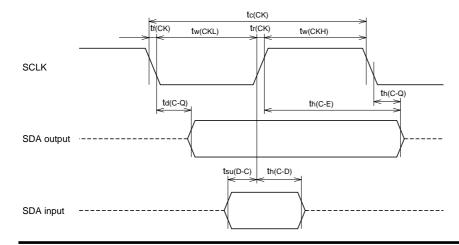
3: When f(XIN) = 25 MHz or less, calculate the minimum value according to formula 3.

Formula 3: $\frac{1 \times 3}{f(XIN)} \times 10^9$

4: When f(XIN) = 25 MHz or less, calculate the minimum value according to formula 4

Formula 4: $\frac{1 \times 5}{f(XIN)} \times 10^9$

AC waveforms



Test conditions for AC characteristics

 \bullet Output timing voltage : VoL = 0.8 V, VoH = 2.0 V

• Input timing voltage : VIL = 0.2 VCC, VIH = 0.8 VCC







Flash memory mode 3 (CPU reprogramming mode)

The M37753FFCFP and the M37753FFCHP have the CPU reprogramming mode where a built-in flash memory is handled by the central processing unit (CPU). 112 Kbytes (addresses 00100016 to 00EFFF16 and addresses 01100016 to 01EFFF16) of the 120-Kbyte flash memory shown in Figure 1 can be reprogrammed (erase and program). Remaining 8 Kbytes of the flash memory (addresses 00F00016 to 010FFF16) cannot be reprogrammed, but can be read. (It is possible to reprogram this remaining 8 Kbytes in the parallel I/O mode and the serial I/O mode). This area of 8 Kbytes can be used as an area where the control program of CPU reprogramming mode is stored

In CPU reprogramming mode, the flash memory is handled by writing and reading to/from the flash memory control register (see Figure 21) and the flash command register (see Figure 22).

The CNVss pin is used as the VPP power supply pin in CPU reprogramming mode. It is necessary to apply the power-supply voltage of VPPH from the external to this pin.

Functional outline (Parallel input/output mode)

Figure 21 shows the flash memory control register bit configuration.

Figure 22 shows the flash command register bit configuration.

Bit 0 of the flash memory control register is the CPU reprogramming mode select bit. When this bit is set to "1" and VPPH is applied to the CNVss/VPP pin, the CPU reprogramming mode is selected. Whether the CPU reprogramming mode is realized or not is judged by reading the CPU reprogramming mode monitor flag (bit 3 of the flash memory control register).

Bit 1 is a busy flag which becomes "1" during auto erase, erase, and program execution.

Whether these operations have been completed or not is judged by checking this flag after each command of auto erase, erase, and the program is executed.

Bits 4, 5 of the flash memory control register are the erase/program area select bits. These bits specify an area where auto erase, erase, and program is operated. When the auto erase and the erase commands are executed after an area is specified by these bits, only the specified area is erased. Only for the specified area, programming is enabled; for the other areas, programming is disabled.

Figure 23 shows the processor mode register 0 bit configuration in the CPU reprogramming mode. Set bit 1 to "0" (single-chip or memory expansion mode) in the CPU reprogramming mode. Set bit 2 (internal memory access bus cycle select bit) to "0."

Be sure to set data length select flag m to "1" (8-bit length) beforehand because writing and reading of data are operated in unit of byte.

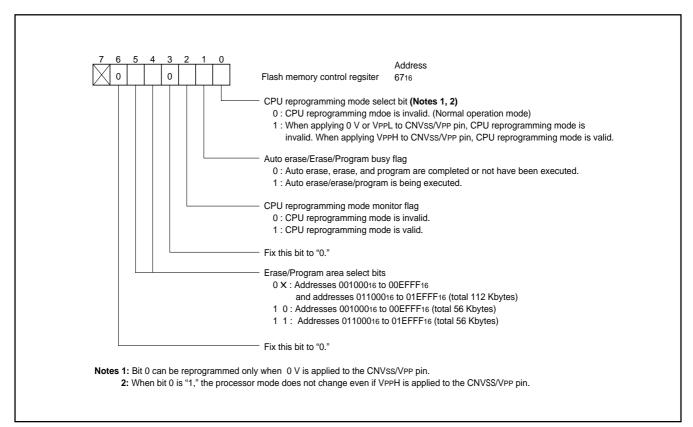


Fig. 21 Flash memory control register bit configuration







CPU reprogramming mode operation procedure

The operation procedure in CPU reprogramming mode is described below.

- < Beginning procedure >
- ① Apply 0 V to the CNVss/VPP pin for reset release.
- 2 Set the processor mode register 0 (see Figure 23).
- ③ After CPU reprogramming mode control program is transferred to internal RAM, jump to this control program on RAM. (The following operations are controlled by this control program).
- 4 Set "1" (8-bit length) to data length select flag m.
- ⑤ Set "1" to the CPU reprogramming mode select bit.
- 6 Apply VPPH to the CNVss/VPP pin.
- Read the CPU reprogramming mode monitor flag to confirm whether the CPU reprogramming mode is valid.
- ® The operation of the flash memory is executed by software-command-writing to the flash command register.

Note: The following are necessary other than this:

- •Control for data which is input from the external (serial I/O etc.) and to be programmed to the flash memory
- •Initial setting for ports etc.
- •Writing to the watchdog timer

- < Release procedure >
- ① Apply 0V to the CNVss/VPP pin.
- 2 Set the CPU reprogramming mode select bit to "0."

Each software command is explained as follows.

Read command

When "0016" is written to the flash command register, the M37753FFCFP and the M37753FFCHP enter the read mode. The contents of the corresponding address can be read by reading the flash memory (For instance, with the LDA instruction etc.) under this condition.

The read mode is maintained until another command code is written to the flash command register. Accordingly, after setting the read mode once, the contents of the flash memory can continuously be read

After reset and after the reset command is executed, the read mode is set

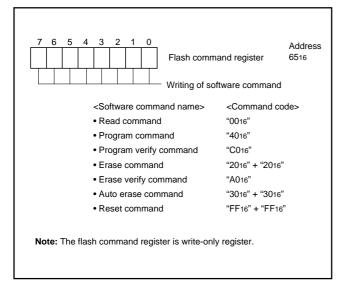


Fig. 22 Flash command register bit configuration

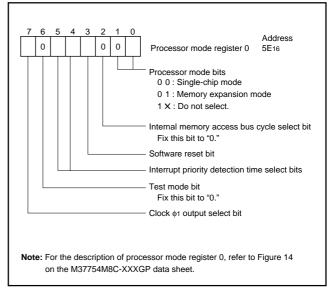


Fig. 23 Processor mode register 0 bit configuration in CPU rewriting mode







Program command

When "4016" is written to the flash command register, the M37753FFCFP and the M37753FFCHP enter the program mode. Subsequently to this, if the instruction (for instance, STA or LDM instruction) for writing byte data in the address to be programmed is executed, the control circuit of the flash memory executes the program. The auto erase/erase/program busy flag of the flash memory control register is set to "1" when the program starts, and becomes "0" when the program is completed. Accordingly, after the write instruction is executed, CPU can recognize the completion of the program by polling this bit.

The programmed area must be specified beforehand by the erase/ program area select bits.

During programming, watchdog timer stops with "FFF16" set.

Note: A programming operation is not completed by executing the program command once. Always be sure to execute a program verify command after executing the program command. When the failure is found in this verification, the user must repeatedly execute the program command until the pass. Refer to Figure 24 for the flow chart of the programming.

Program verify command

When "C016" is written to the flash command register, the M37753FFCFP and the M37753FFCHP enter the program verify mode. Subsequently to this, if the instruction (for instance, LDA instruction) for reading byte data from the address to be verified (i.e., previously programmed address), the contents which has been written to the address actually is read.

CPU compares this read data with data which has been written by the previous program command. In consequence of the comparison, if not agreeing, the operation of "program \rightarrow program verify" must be executed again.

Erase command

When writing "2016" twice continuously to the flash command register, the flash memory control circuit performs erase to the area specified beforehand by the erase/program area select bits.

Auto erase/erase/program busy flag of the flash memory control register becomes "1" when erase begins, and it becomes "0" when erase completes. Accordingly, CPU can recognize the completion of erase by polling this bit.

Data "0016" must be written to all areas to be erased by the program and the program verify commands before the erase command is executed

During programming, watchdog timer stops with "FFF16" set.

Note: The erasing operation is not completed by executing the erase command once. Always be sure to execute an erase verify command after executing the erase command. When the failure is found in this verification, the user must repeatedly execute the erase command until the pass. Refer to Figure 24 for the erasing flowchart.

Erase verify command

When "A016" is written to the flash command register, the M37753FFCFP and the M37753FFCHP enter the erase verify mode. Subsequently to this, if the instruction (for instance, LDA instruction) for reading byte data from the address to be verified, the contents of the address is read.

CPU must erase and verify to all erased areas in a unit of address. If the address of which data is not "FF16" (i.e., data is not erased) is found, it is necessary to discontinue erasure verification there, and execute the operation of "erase \rightarrow erase verify" again.

Note: By executing the operation of "erase →erase verify" again when the memory not erased is found. It is unnecessary to write data "0016" before erasing in this case.





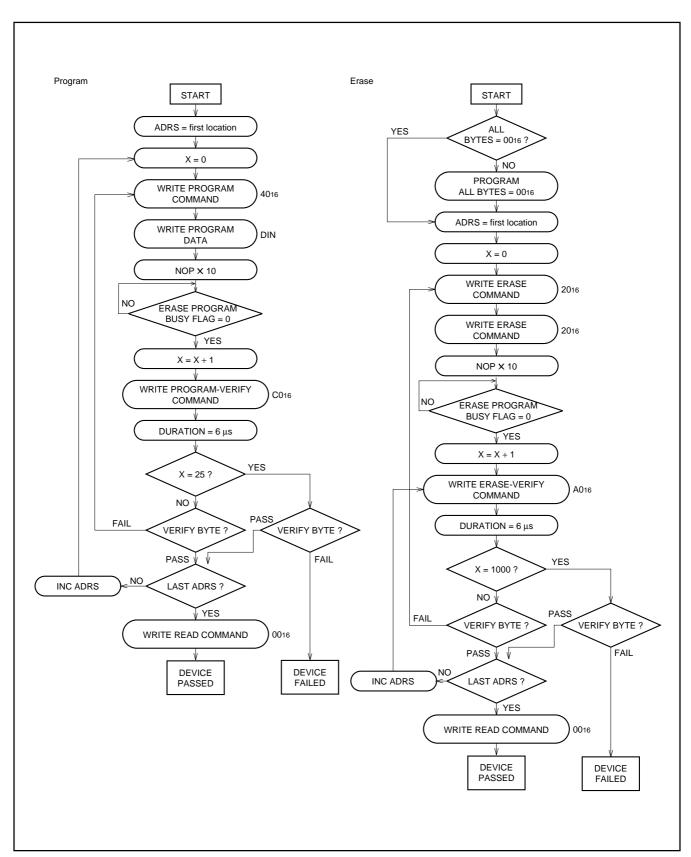


Fig. 24 Flowchart when program/erase/auto erase is executed (1)







Auto erase command

When writing "3016" twice continuously to the flash command register, the flash memory control circuit executes the auto erase sequence described below for the area specified beforehand by the erase/program area select bits.

- (1) Data "0016" is written to the area to be erased in the flash memory.
- (2) The erasure is executed.
- (3) The contents of the erased flash memory is erase-verified one by one. When the address which is not erased is found, verification is interrupted, and after the erase command is executed again, erase-verification is operated again.
- (4) When the erasure of all areas specified to be erased, is confirmed by erase-verify-operation, the auto erase command is ended

The auto erase/erase/program busy flag of the flash memory control register becomes "1" when auto erase starts, and becomes "0" when auto erase completes. Accordingly, CPU can recognize the completion of auto erase by polling this bit.

During auto erase, watchdog timer stops with "FF16" set.

Note: When the flash memory is erased by using the auto erase command, it is unnecessary to execute the erase and erase verify commands. Figure 25 shows the flowchart when auto erase is executed.

DC electric characteristics

Note: The characteristic of the flash memory part are the same as the standard of the parallel I/O mode.

AC electric characteristics

Note: The characteristics are the same as the standards of the microcomputer mode.

Reset command

The reset command is a command to discontinue the program, erase, or the auto erase command on the way. When "FF16" is written to the command register two times continuously after "4016," "2016," or "3016" is written to the flash command register, the program, erase, or auto erase command becomes invalid (reset), and the M37753FFCFP and the M37753FFCHP enters the reset mode. The contents of the memory does not change even if the reset command is executed.

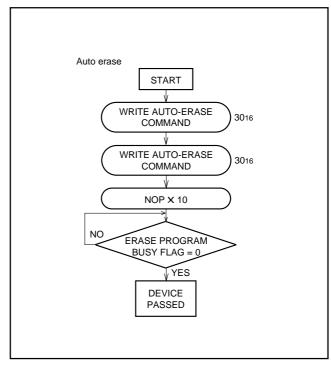


Fig. 25 Flowchart when program/erase/auto erase is executed (2)







ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Ratings	Unit
Vcc	Power source voltage	-0.3 to 7	V
AVcc	Analog power source voltage	-0.3 to 7	V
VI	Input voltage RESET, CNVss, BYTE	-0.3 to 12 (Note)	V
Vı	Input voltage P00–P07, P10–P17, P20–P27, P30–P33, P40–P47, P50–P57, P60–P67, P70–P77, P80–P87, VREF, XIN	-0.3 to Vcc+0.3	V
Vo	Output voltage P00–P07, P10–P17, P20–P27, P30–P33, P40–P47, P50–P57, P60–P67, P70–P77, P80–P87, Xout, Ē	-0.3 to Vcc+0.3	V
Pd	Power dissipation	300	mW
Topr	Operating temperature	–20 to 85	°C
Tstg	Storage temerature	-40 to 150	°C

Note: For the CNVss pin, this is 12.6V when programming to the flash memory.

RECOMMENDED OPERATING CONDITIONS (Vcc = 5 V±10 %, Ta = -20 to 85 °C, unless otherwise noted)

Symbol	Parameter	Limits			11
		Min.	Тур.	Max.	Unit
Vcc	Supply voltage	4.5	5.0	5.5	V
AVcc	Analog supply voltage		Vcc		V
Vss	Supply voltage		0		V
AVss	Analog supply voltage		0		V
ViH	High-level input voltage P00–P07, P30–P33, P40–P47, P50–P57, P60–P67, P70–P77, P80–P87, XIN, RESET, CNVss, BYTE	0.8 Vcc		Vcc	٧
VIH	High-level input voltage P10-P17, P20-P27 (in single-chip mode)	0.8 Vcc		Vcc	V
ViH	High-level input voltage P10–P17, P20–P27 (in memory expansion mode and microprocessor mode)	0.5 Vcc		Vcc	٧
VIL	Low-level input voltage P00–P07, P30–P33, P40–P47, P50–P57, P60–P67, P70–P77, P80–P87, XIN, RESET, CNVss, BYTE	0		0.2 Vcc	V
VIL	Low-level input voltage P10-P17, P20-P27 (in single-chip mode)	0		0.2 Vcc	V
VIL	Low-level input voltage P10–P17, P20–P27 (in memory expansion mode and microprocessor mode)	0		0.16 Vcc	V
IOH(peak)	High-level peak output current P00–P07, P10–P17, P20–P27, P30–P33, P40–P47, P50–P57, P60–P67, P70–P77, P80–P87			-10	mA
IOH(avg)	High-level average output current P00–P07, P10–P17, P20–P27, P30–P33, P40–P47, P50–P57, P60–P67, P70–P77, P80–P87			-5	mA
IOL(peak)	Low-level peak output current P00–P07, P10–P17, P20–P27, P30–P33, P40–P47, P56, P57, P60–P67, P70–P77, P80–P87			10	mA
IOL(peak)	Low-level peak output current P50–P55			20	mA
IOL(avg)	Low-level average output current P00–P07, P10–P17, P20–P27, P30–P33, P40–P47, P56, P57, P60–P67, P70–P77, P80–P87			5	mA
IOL(avg)	Low-level average output current P50–P55			15	mA
f(XIN)	External clock frequency input (Note 3) Low-speed running			25	NAL I-
	High-speed running			40	MHz

Notes 1: Average output current is the average value of a 100 ms interval.

- 2: The sum of IOL(peak) for ports P0, P1, P2, P3, and P8 must be 80 mA or less, the sum of IOH(peak) for ports P0, P1, P2, P3, and P8 must be 80 mA or less, the sum of IOH(peak) for ports P4, P5, P6, and P7 must be 110 mA or less, the sum of IOH(peak) for ports P4, P5, P6, and P7 must be 80 mA or less.
- 3: When the clock source select bit is "1," f(XIN)'s maximum limit is 12.5 MHz at low-speed running and is 20 MHz at high-speed







ELECTRICAL CHARACTERISTICS (Vcc = 5 V, Vss = 0 V, Ta = -20 to 85 °C, f(XIN) = 40 MHz (Note))

Symbol	Parameter	Test conditions	<u> </u>	Limits		Unit
Cymbol	i alametei	Test corraitions	Min.	Тур.	Max.	Offic
Vон	High-level output voltage P00–P07, P10–P17, P20–F P30, P31, P33, P40–P47, P50–P57, P60–P67, P70–F P80–P87	Ιου - 10 mΔ	3			V
Voн	High-level output voltage P00–P07, P10–P17, P20–F P30, P31, P33,	P27, IOH = $-400 \ \mu A$	4.7			V
Voн	High-level output voltage P32	Iон = −10 mA	3.1			.,
VOH		IOH = $-400 \mu A$	4.8			V
Vон	High-level output voltage E	IOH = -10 mA	3.4			V
		IOH = -400 μA	4.8			v
VoL	Low-level output voltage P00–P07, P10–P17, P20–I P30, P31, P33, P40–P47, P56, P57, P60–P67,P70–F P80–P87	Ιοι – 10 mA			2	V
VoL	Low-level output voltage P00–P07, P10–P17, P20–l P30, P31, P33	P27, IOL = 2 mA			0.45	V
Vol	Low-level output voltage P32	IOL = 10 mA			1.9	V
VOL		IOL = 2 mA			0.43	V
Vol	Low-level output voltage \overline{E}	IOL = 10 mA			1.6	V
VOL		IOL = 2 mA			0.4	V
Vol	Low-level output voltage P50–P55	IOL = 20 mA			2	V
		IOL = 2 mA			0.4	v
VT+ —VT-	Hysteresis HOLD, RDY, TA0IN-TA4IN, TB0IN-TB2IN, INT0-INT4, ADTRG, CTS0, CTS1, CLK0, CLK1, RxD0, RxD1		0.4		1	V
VT+ —VT-	Hysteresis RESET, HOLD, RDY		0.2		0.5	V
VT+ —VT-	Hysteresis XIN		0.1		0.3	V
lін	High-level input current P00–P07, P10–P17, P20–P2 P30–P33, P40–P47, P50–P5 P60–P67, P70–P77, P80–P8 XIN, RESET, CNVss, BYTE	7, 7, VI = 5 V			5	μΑ
lıL	Low-level input current P00–P07, P10–P17, P20–P2 P30–P33, P40–P47, P50–P5 P60–P67, P70–P77, P81–P8 XIN, RESET, CNVss, BYTE	3, \\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\			-5	μΑ
lu .	Low-level input current P54-P57, P80	VI = 0 V, No pull-up trans	sistor		-5	μΑ
liL		VI = 0 V, Pull-up transiste		-0.5	-1.0	mA
VRAM	RAM hold voltage	When clock is stoped.	2			V
	Power supply current (target value)	open and other waveform	` '	25	50	mA
Icc		reset. is stoppe			1	μA
		Ta = 85 °C is stoppe	C when clcock d.		20	μΑ

Note: f(XIN) = 20 MHz when the clock source select bit = "1."







A-D CONVERTER CHARACTERISTICS

(Vcc = AVcc = 5 V ± 10 %, Vss = AVss = 0 V, Ta = -20 to 85 °C, the clock source select bit = 0, unless otherwise noted)

			T			Limits		
Symbol	Parameter Test conditions		Min.	Тур.	Max.	Unit		
	Resolution	D 1 5		A-D converter selected			10	Bits
	Resolution	VREF = VCC		Comparator selected			1 256 VREF	V
				10-bit mode			± 3	LSB
			250 kHz ≤ <i>φ</i> AD ≤ 12.5 MHz	8-bit mode			± 2	LSB
	Absolute accuracy	VREF = VCC	≥ 12.3 IVITZ	Comparator			± 40	mV
		8-bit mode			± 3	LSB		
			20 MHz (Note 1)	Comparator			± 60	mV
RLADDER	Ladder resistance	VREF = VCC			5		20	kΩ
	High-speed	ϕ AD = f(XIN)/4	10-bit mode	5.9				
			8-bit mode	4.9]	
		running	Colociou	Comparator	1.4]
tCONV	Conversion time	(f(XIN) ≤ 40 MHz)	ϕ AD = f(XIN)/2	8-bit mode	2.45			μs
		(Note 2)	selected	Comparator	0.7			"
				10-bit mode	4.72]
		Low-speed runn		8-bit mode	3.92]
		(f(XIN) ≤ 25 MHz		Comparator	1.12]
VREF	Reference voltage				2.7		Vcc	V
VIA	Analog input voltage				0		VREF	V

Notes 1: This is valid when the high-speed running is selected.

D-A CONVERTER CHARACTERISTICS

(VCC = 5 V, VSS = AVSS = 0 V, VREF = 5 V, Ta = -20 to 85 °C, unless otherwise noted)

Symbol	Parameter	Took oon dikinga		Limits		
		Test conditions	Min.	Тур.	Max.	Unit
	Resolution				8	Bits
	Absolute accuracy				± 1.0	%
tsu	Set time				3	μs
Ro	Output resistance		1	2.5	4	kΩ
IVREF	Reference power supply input current	(Note)			3.2	mA

Note: The test conditions are as follows:

- One D-A converter is used.
- The D-A register value of the unused D-A converter is "0016."
- The reference power supply input current of the ladder resistance of the A-D converter is excluded.



^{2:} When the clock source select bit = 1, f(XIN) is 20 MHz or less at the high-speed running, and f(XIN) is 12.5 MHz or less at the low-speed running.



SHINGLE-CHIP 16-BIT CMOS MICROCOMPUTER FLASH MEMORY VERSION

PERIPHERAL DEVICE INPUT/OUTPUT TIMING (Vcc = 5 V±10 %, Vcc = 0 V, Ta = -20 to 85 °C, unless otherwise noted)

- * If the values depends on external clock frequency f(XIN), formulas of the limits are shown below. Also, the values at f(XIN) = 40 MHz in high-speed running and at f(XIN) = 25 MHz in low-speed running are shown in (). At this time, the clock source select bit is "0." When the clock source select bit is "1", regard f(XIN) in tables as 2-f(XIN).
- * The rise and fall time of input signal must be 100 ns or less respectively, unless otherwise noted.

Timer A input (Count input in event counter mode)

Symbol	Parameter -		Limits		
			Max.	Unit	
tc(TA)	TAilN input cycle time	80		ns	
tw(TAH)	TAilN input high-level pulse width	40		ns	
tw(TAL)	TAin input low-level pulse width	40		ns	

Timer A input (Gating input in timer mode)

Coursels al	Darameter		Lin	nits	I lait
Symbol	Parameter	Parameter		Max.	Unit
1.(70)	TAilN input cycle time	f(XIN) ≤ 40 MHz	$\frac{16 \times 10^9}{f(X_{IN})}$ (400)		ns
tc(TA)		(XIN) ≤ 25 MHz	$\frac{8 \times 10^9}{f(X_{IN})}$ (320)		ns
tw(TAH)	TAilN input high-level pulse width	f(XIN) ≤ 40 MHz	$\frac{8 \times 10^9}{f(XIN)}$ (200)		ns
tw(IAH)		f(XIN) ≤ 25 MHz	$\frac{4 \times 10^9}{f(XIN)}$ (160)		ns
tw(TAL)	TAilN input low-level pulse width	f(XIN) ≤ 40 MHz	$\frac{8 \times 10^9}{f(XIN)}$ (200)		ns
tw(IAL)		f(XIN) ≤ 25 MHz	$\frac{4 \times 10^9}{f(X_{IN})}$ (160)		ns

Note: The TAim input cycle time requires 4 or more cycles of count source. The TAim input high-level pulse width and the TAim input low-level pulse width respectively require 2 or more cycles of the count source. The limits in the table are the values when the count source is f(XIN)/4 in high-speed running (f(XIN) ≤ 40 MHz) and when the count source is f(XIN)/2 in low-speed running (f(XIN) ≤ 25 MHz). At this time, the clock source select bit is "0."

Timer A input (External trigger input in one-shot pulse mode)

Courselle al	Parameter		Lin	Llait	
Symbol			Min.	Max.	Unit
tc(TA)	TAiıN input cycle time	f(XIN) ≤ 40 MHz	$\frac{8\times10^9}{f(XIN)}$ (200)		ns
LO(1A)	n and input dybic time	f(XIN) ≤ 25 MHz	$\frac{4 \times 10^9}{f(XIN)} (160)$		ns
tw(TAH)	TAilN input high-level pulse width		80		ns
tw(TAL)	TAilN input low-level pulse width		80		ns

Timer A input (External trigger input in pulse width modulation mode)

Symbol	Parameter -		Limits		
			Max.	Unit	
tw(TAH)	TAilN input high-level pulse width	80		ns	
tw(TAL)	TAilN input low-level pulse width	80		ns	

Timer A input (Up-down input in event counter mode)

Symbol	Parameter		Limits		
			Max.	Unit	
tc(UP)	TAiout input cycle time	2000		ns	
tw(UPH)	TAiout input high-level pulse width	1000		ns	
tw(UPL)	TAiout input low-level pulse width	1000		ns	
tsu(UP-Tɪn)	TAiout input setup time	400		ns	
th(TIN-UP)	TAiout input hold time	400		ns	



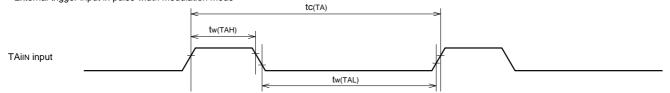




Timer A input (Two-phase pulse input in event counter mode)

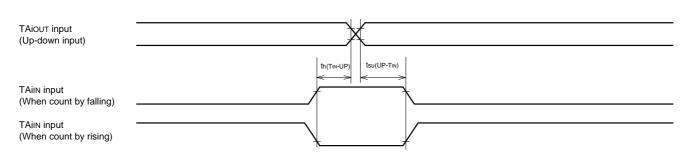
Symbol	.		Limits		
	Parameter	Min.	Max.	Unit	
tc(TA)	TAilN input cycle time	800		ns	
tsu(TAjIN-TAjOUT)	TAjın input setup time	200		ns	
tsu(TAjout-TAjin)	TAjout input setup time	200		ns	

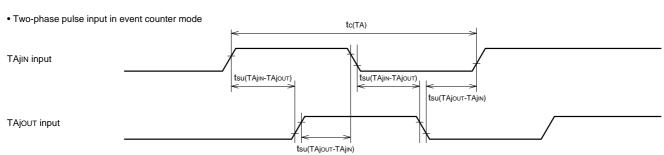
- Count input in event counter mode
- Gating input in timer mode
- External trigger input in one-shot pulse mode
 External trigger input in pulse width modulation mode



• Up-down and count input in event counter mode







Test conditions

- Vcc = 5 V±10 %
- Input timing voltage : VIL = 1.0 V, VIH = 4.0 V







Timer B input (Count input in event counter mode)

Symbol	Parameter		Limits		
			Max.	Unit	
tc(TB)	TBiln input cycle time (one edge count)	80		ns	
tw(TBH)	TBiln input high-level pulse width (one edge count)	40		ns	
tw(TBL)	TBiln input low-level pulse width (one edge count)	40		ns	
tc(TB)	TBiln input cycle time (both edge count)	160		ns	
tw(TBH)	TBiln input high-level pulse width (both edge count)	80		ns	
tw(TBL)	TBilN input low-level pulse width (both edge count)	80		ns	

Timer B input (Pulse period measurement mode)

O make at	Parameter		Lin	nits	1.1
Symbol			Min.	Max.	Unit
1 (77)	TBilN input cycle time	f(XIN) ≤ 40 MHz	$\frac{16 \times 10^9}{f(XIN)}$ (400)		ns
tc(TB)		f(XIN) ≤ 25 MHz	$\frac{8 \times 10^9}{f(XIN)}$ (320)		ns
tw(TBH)	ТВіі input high-level pulse width	f(XIN) ≤ 40 MHz	$\frac{8 \times 10^9}{f(XIN)}$ (200)		ns
tw(TBH)		f(XIN) ≤ 25 MHz	$\frac{4 \times 10^9}{f(XIN)}$ (160)		ns
tw(TBL)	TBilN input low-level pulse width	f(XIN) ≤ 40 MHz	$\frac{8 \times 10^9}{f(XIN)}$ (200)		ns
IW(IDL)		f(XIN) ≤ 25 MHz	$\frac{4 \times 10^9}{f(XIN)}$ (160)		ns

Note: The TBiIN input cycle time requires 4 or more cycles of count source. The TBiIN input high-level pulse width and the TBiIN input low-level pulse width respectively require 2 or more cycles of the count source. The limits in the table are the values when the count source is f(XIN)/4 in high-speed running (f(XIN) ≤ 40 MHz) and when the count source is f(XIN)/2 in low-speed running (f(XIN) ≤ 25 MHz). At this time, the clock source select bit is "0."

Timer B input (Pulse width measurement mode)

Currele el	Parameter		Limits		I lait
Symbol			Min.	Max.	Unit
1 (77)	TBiIN input cycle time	f(XIN) ≤ 40 MHz	$\frac{16 \times 10^9}{f(XIN)}$ (400)		ns
tc(TB)		f(XIN) ≤ 25 MHz	$\frac{8 \times 10^9}{f(XIN)}$ (320)		ns
tw(TBH)	ТВіін input high-level pulse width	f(XIN) ≤ 40 MHz	$\frac{8 \times 10^9}{f(XIN)}$ (200)		ns
tw(TDH)		f(XIN) ≤ 25 MHz	$\frac{4 \times 10^9}{f(XIN)}$ (160)		ns
tw/TPL)	TBilN input low-level pulse width	f(XIN) ≤ 40 MHz	$\frac{8 \times 10^9}{f(XIN)}$ (200)		ns
tw(TBL)		f(XIN) ≤ 25 MHz	$\frac{4 \times 10^9}{f(XIN)}$ (160)		ns

Note: The TBin input cycle time requires 4 or more cycles of count source. The TBin input high-level pulse width and the TBin input low-level pulse width respectively require 2 or more cycles of the count source. The limits in the table are the values when the count source is f(XIN)/4 in high-speed running $(f(XIN) \le 40 \text{ MHz})$ and when the count source is f(XIN)/2 in low-speed running $(f(XIN) \le 25 \text{ MHz})$. At this time, the clock source select bit is "0."

A-D trigger input

Symbol	Devender	Lim	1.126	
	Parameter	Min.	Max.	Unit
tc(AD)	ADTRG input cycle time (minimum allowable trigger)	1000		ns
tw(ADL)	ADTRG input low-level pulse width	125		ns





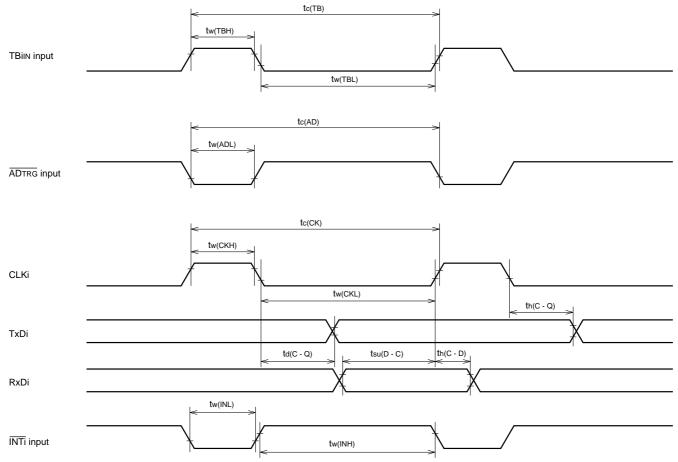


Serial I/O

Symbol	D	Lin	1.1-26	
	Parameter		Max.	Unit
tc(CK)	CLKi input cycle time	200		ns
tw(CKH)	CLKi input high-level pulse width	100		ns
tw(CKL)	CLKi input low-level pulse width	100		ns
td(C-Q)	TxDi output delay time		80	ns
th(C-Q)	TxDi hold time	0		ns
tsu(D-C)	RxDi input setup time	20		ns
th(C-D)	RxDi input hold time	90		ns

External interrupt INTi input

Symbol	Deventer		Limits		
	Parameter	Min.	Max.	Unit	
tw(INH)	INTi input high-level pulse width	250		ns	
tw(INL)	INTi input low-level pulse width	250		ns	



Test conditions

- Input timing voltage: VIL = 1.0 V, VIH = 4.0 V
 Output timing voltage: VOL = 0.8 V, VOH = 2.0 V, CL = 100 pF





SHINGLE-CHIP 16-BIT CMOS MICROCOMPUTER FLASH MEMORY VERSION

READY, HOLD TIMING

Timing requirements (VCC = 5 V \pm 10 %, VSS = 0 V, Ta = -20 to 85 °C, f(XIN) = 40 MHz when the clock source select bit = "0"*, unless otherwise noted)

* The rise and fall time of input signal must be 100 ns or less respectively, unless otherwise noted.

Symbol	Demonstra	Lin	11-2	
	Parameter		Max.	Unit
tsu(RDY-φ1)	RDY input setup time	42		ns
tsu(HOLD-φ1)	HOLD input setup time	42		ns
th(ϕ 1-RDY)	RDY input hold time	0		ns
th(ϕ 1-HOLD)	HOLD input hold time	0		ns

^{*}: f(XIN) = 20 MHz when the clock source select bit = "1".

Switching characteristics (Vcc = 5 V \pm 10 %, Vss = 0 V, Ta = -20 to 85 °C, f(XIN) = 40 MHz when the clock source select bit = "0"*, unless otherwise noted)

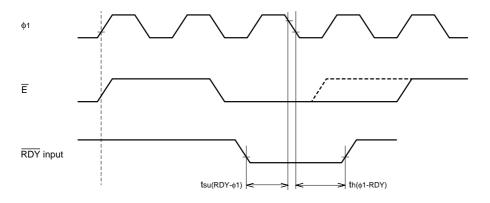
O made at	Dono martino	Lin	l lait		
Symbol	Parameter	Min.	Max.	Unit	
td(∳1-HLDA)	HLDA output delay time		50	ns	
tpxz(HLDA-R/WZ)	Floating start delay time (at hold state)		50	ns	
tpxz(HLDA-BHEZ)	Floating start delay time (at hold state)		50	ns	
tpxz(HLDA-AZ)	Floating start delay time (at hold state)		50	ns	
tpxz(HLDA-A/DZ)	Floating start delay time (at hold state)		50	ns	
tpzx(HLDA-R/WZ)	Floating release delay time (at hold state)	0		ns	
tpzx(HLDA-BHEZ)	Floating release delay time (at hold state)	0		ns	
tpzx(HLDA-AZ)	Floating release delay time (at hold state)	0		ns	
tpzx(HLDA-A/DZ)	Floating release delay time (at hold state)	0		ns	

^{*}: f(XIN) = 20 MHz when the clock source select bit = "1".



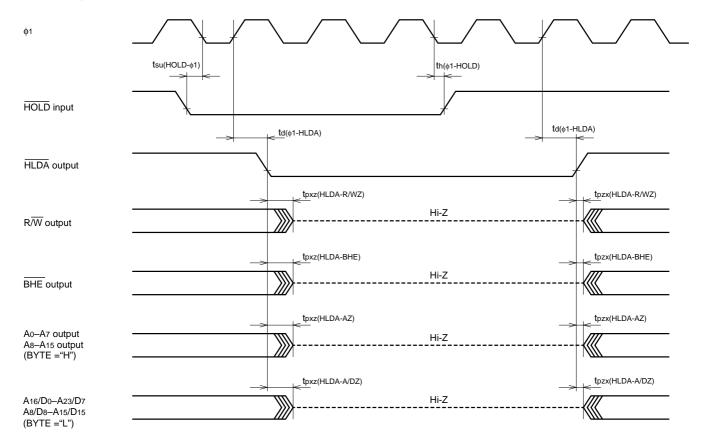


RDY input (when 3-*φ* access in high-speed running)



* RDY input is always sampled at the falling edge of \$1 just before the E signal's rise regardless of the bus mode and the number of waits.

HOLD input



Test conditions

- Vcc = 5 V±10 %
- \overline{RDY} input, \overline{HOLD} input : VIL = 1.0 V, VIH = 4.0 V
- $\overline{\text{HLDA}}$ output : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF





SHINGLE-CHIP 16-BIT CMOS MICROCOMPUTER FLASH MEMORY VERSION

Timing requirements (Vcc = 5 V±10 %, Vss = 0 V, Ta = -20 to 85 °C, f(XIN) = 40 MHz when the clock source select bit = "0"*, unless otherwise noted)

* The rise and fall time of input signal must be 100 ns or less respectively, unless otherwise noted.

Single-chip mode

Symbol	Parameter	Lin	1.121	
		Min.	Max.	Unit
tc	External clock input cycle time (Note 1)	25		ns
tw(H)	External clock input high-level pulse width (Note 2)	tc/2 - 8		ns
tw(L)	External clock input low-level pulse width (Note 2)	tc/2 - 8		ns
tr	External clock rise time		8	ns
tf	External clock fall time		8	ns
tsu(PiD-E)	Port Pi input setup time (i = 0—8)	60		ns
th(E-PiD)	Port Pi input hold time (i = 0—8)	0		ns

^{*:} f(XIN) = 20 MHz when the clock source select bit = "1"

Notes 1: When the clock source select bit = "1", tc's minimum limit is 50 ns.

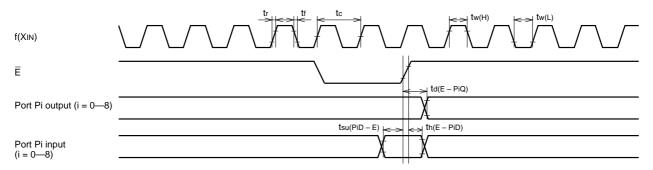
2: When the clock source select bit = "1", set tw(H)/tc and tw(L)/tc ratios to 45 to 55 %.

Switching characteristics (VCC = 5 V±10 %, VSS = 0 V, Ta = -20 to 85 °C, f(XIN) = 40 MHz when the clock source select bit = "0"*, unless otherwise noted)

(Single-chip mode)

	0	Danasastas	Lin	nits	1.1	
Symbol	Parameter	Min.	Max. Uni		l	
	td(E-PiQ)	Port Pi data output delay time (i = 0—8)		60	ns	l

*: f(XIN) = 20 MHz when the clock source select bit = "1"



Test conditions

- VCC = 5 V+10 %
- Intput timing voltage : VIL = 1.0 V, VIH = 4.0 V
- Output timing voltage : VOL = 0.8 V, VOH = 2.0 V, CL = 100 pF





SHINGLE-CHIP 16-BIT CMOS MICROCOMPUTER FLASH MEMORY VERSION

Timing requirements (Vcc = 5 V±10 %, Vss = 0 V, Ta = -20 to 85 °C, f(XIN) = 25 MHz when the clock source select bit = "0"*, unless otherwise noted)

* The rise and fall time of input signal must be 100 ns or less respectively, unless otherwise noted.

Memory expansion and Microprocessor mode: Low-speed running

	Parameter	Lir	Lloit	
Symbol		Min.	Max.	Unit
tc	External clock input cycle time (Note 1)	40		ns
tw(H)	External clock input high-level pulse width (Note 2)	tc/2 - 8		ns
tw(L)	External clock input low-level pulse width (Note 2)	tc/2 - 8		ns
tr	External clock rise time		8	ns
tf	External clock fall time		8	ns
tsu(D-E)	Data input setup time	30		ns
tsu(PiD-E)	Port Pi input setup time (i = 4—8)	60		ns
th(E-D)	Data input hold time	0		ns
th(E-PiD)	Port Pi input hold time (i = 4—8)	0		ns
			55 (2-φ access)	
tsu(An/A-D)	Data setup time with address stabilized (Note 3)		135 (3-ø access)	ns
			215 (4-ø access)	

^{*:} f(XIN) = 12.5 MHz when the clock source selet bit = "1"

Notes 1: When the clock source select bit = "1", tc's minimum limit is 80 ns.

- 2: When the clock source select bit = "1", set tw(H)/tc and tw(L)/tc ratios to 45 to 55 %.
- **3:** Since the values depend on external clock input frequency f(XIN), calculate them using the bus timing data formula on the page after the next page.





SHINGLE-CHIP 16-BIT CMOS MICROCOMPUTER FLASH MEMORY VERSION

Switching characteristics (Vcc = 5 V±10 %, Vss = 0 V, Ta = -20 to 85 °C, f(XIN) = 25 MHz when the clock source select bit = "0"*, unless otherwise noted)

Memory expansion and Microprocessor mode: Low-speed running

0	Devenuetos	2-φ a	2-φ access		3-¢ access		4-φ access	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tw(φH), tw(φL)	ϕ high-level pulse width, ϕ low-level pulse width (Note)	20		20		20		ns
td(E− <i>φ</i> 1)	ϕ 1 output delay time	-12	7	-12	7	-12	7	ns
tw(EL)	E low-level pulse width (Note)	55		135		135		ns
td(An–E)	Address output delay time (Note)	12		12		92		ns
td(E-DQ)	Data output delay time		35		35		35	ns
tpxz(E-DZ)	Floating start delay time		5		5		5	ns
td(A-E)	Address output delay time (Note)	12		12		92		ns
td(A-ALE)	Address output delay time (Note)	5		5		52		ns
td(E-ALE)	ALE output delay time (Note)	20		20		20		ns
td(ALE-E)	ALE output delay time	4		4		4		ns
tw(ALE)	ALE pulse width (Note)	22		22		62		ns
td(BHE-E)	BHE output delay time (Note)	15		15		95		ns
td(R/W-E)	R/W output delay time (Note)	15		15		95		ns
th(E-An)	Address hold time (Note)	10		10		10		ns
th(ALE-A)	Address hold time	9		9		25 (Note)		ns
th(E-DQ)	Data hold time (Note)	18		18		18		ns
tpzx(E-DZ)	Floating release delay time (Note)	18		18		18		ns
th(E-BHE)	BHE hold time (Note)	10		10		10		ns
th(E-R/W)	R/W hold time (Note)	10		10		10		ns
td(E-PiQ)	Port Pi data output delay time (i = 4—8)		60		60		60	ns

^{*:} f(XIN) = 12.5 MHz when the clock source selet bit = "1"

Note: Since the values depend on external clock input frequency f(XIN), calculate them using the bus timing data formula on the next page. The value of t_{ALE-A} depends on $t_$







Bus timing data formulas

Memory expansion and Microprocessor mode : Low-speed running (VCC = $5 \text{ V} \pm 10 \text{ %}$, VSS = 0 V, Ta = -20 to 85 °C, f(XIN) $\leq 25 \text{ MHz}$ when the clock source select bit = "0"*, unless otherwise noted)

Symbol	Parameter	$2-\phi$ access	3-¢ access	4-φ access	Unit
tsu(An/A-D)	Data setup time with address stabilized	$\frac{3 \times 10^9}{f(XIN)}$ -65	$\frac{5 \times 10^9}{f(XIN)}$ -65	$\frac{7\times10^9}{f(XIN)}-65$	ns
$tw(\phiH), tw(\phiL)$	ϕ high-level pulse width, ϕ low-level pulse width	$\frac{1 \times 10^9}{f(XIN)}$ -20	-	-	ns
tw(EL)	E low-level pulse width	$\frac{2 \times 10^9}{f(XIN)}$ -25	$\frac{4\times10^9}{f(XIN)}-25$	-	ns
td(An-E)	Address output delay time	$\frac{1 \times 10^9}{f(XIN)}$ -28	◄	$\frac{3 \times 10^9}{f(XIN)}$ -28	ns
td(A-E)	Address output delay time	$\frac{1 \times 10^9}{f(XIN)}$ -28	-	$\frac{3 \times 10^9}{f(XIN)}$ -28	ns
td(A-ALE)	Address output delay time	$\frac{1 \times 10^9}{f(XIN)}$ -35	-	$\frac{2\times10^9}{f(XIN)}-28$	ns
td(E-ALE)	ALE output delay time	$\frac{1 \times 10^9}{f(XIN)}$ -20	-	-	ns
tw(ALE)	ALE pulse width	$\frac{1\times10^9}{f(XIN)}-18$	-	$\frac{2 \times 10^9}{f(XIN)} - 18$	ns
td(BHE-E)	BHE outupt delay time	$\frac{1 \times 10^9}{f(XIN)}$ -25	-	$\frac{3 \times 10^9}{f(XIN)}$ -25	ns
td(R/W–E)	R/W output delay time	$\frac{1 \times 10^9}{f(XIN)}$ -25	-	$\frac{3 \times 10^9}{f(XIN)}$ -25	ns
th(E-An)	Address hold time	$\frac{1 \times 10^9}{f(XIN)}$ -30	-	-	ns
th(ALE-A)	Address hold time			$\frac{1 \times 10^9}{f(XIN)}$ -15	ns
th(E-DQ)	Data hold time	$\frac{1\times10^9}{f(XIN)}-22$	-	-	ns
tpzx(E-DZ)	Floating release delay time	$\frac{1 \times 10^9}{f(XIN)}$ -22	-	-	ns
td(E-BHE)	BHE hold time	$\frac{1\times10^9}{f(XIN)}-30$	-	-	ns
td(E-R/W)	R/W hold time	$\frac{1 \times 10^9}{f(XIN)}$ -30	-	-	ns

^{*:} $f(XIN) \le 12.5$ MHz when the clock source select bit = "1"

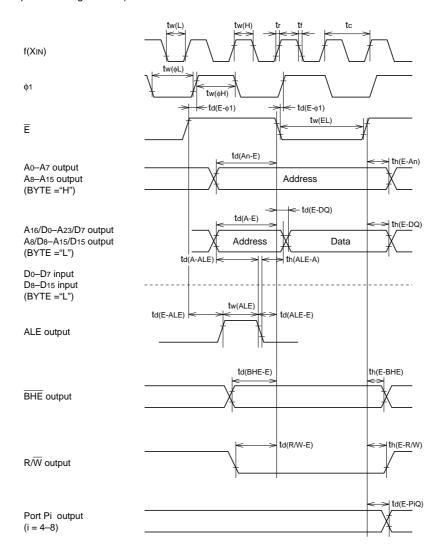
Note: When the clock source select bit is "1", regard f(XIN) in tables as 2-f(XIN).







(when 2-φ access in low-speed running <Write>)



Test conditions (except Port Pi, f(XIN))

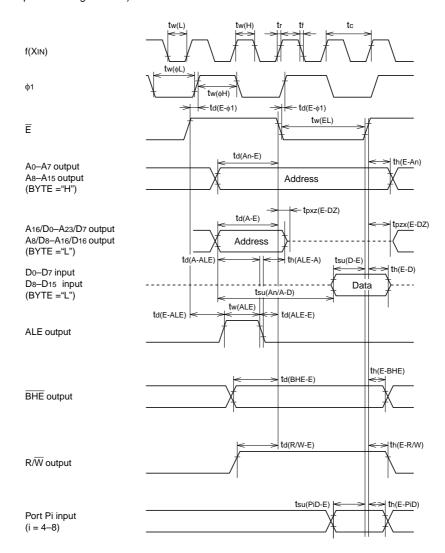
- Vcc = 5 V±10 %
- Output timing voltage : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF
- Data input : VIL = 0.8 V, VIH = 2.5 V

- Vcc = 5 V±10 %
- Input timing voltage : VIL = 1.0 V, VIH = 4.0 V
- \bullet Output timing voltage : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF





(when 2-\$\phi\$ access in low-speed running <Read>)



Test conditions (except Port Pi, f(XIN))

• Vcc = 5 V±10 %

 \bullet Output timing voltage : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF

• Data input : VIL = 0.8 V, VIH = 2.5 V

Test conditions (Port Pi, f(XIN))
• VCC = 5 V±10 %

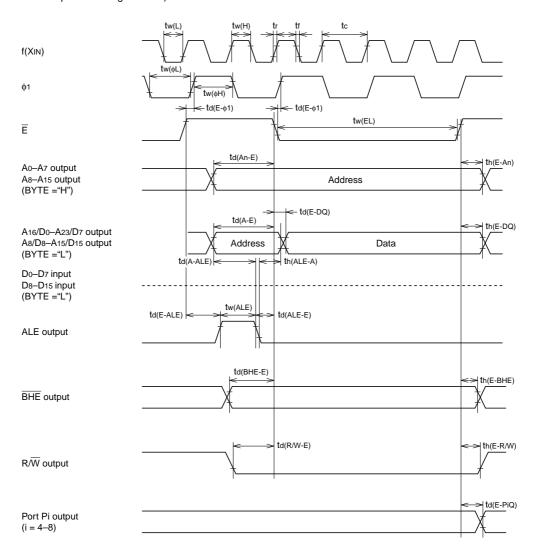
Input timing voltage: Vil = 1.0 V, ViH = 4.0 V
Output timing voltage: Vol = 0.8 V, Voh = 2.0 V, Cl = 100 pF







(when $3-\phi$ access in low-speed running <Write>)



Test conditions (except Port Pi, f(XIN))

• Vcc = 5 V±10 %

• Output timing voltage : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF • Data input : VIL = 0.8 V, VIH = 2.5 V

Test conditions (Port Pi, f(XIN))

• Vcc = 5 V±10 %

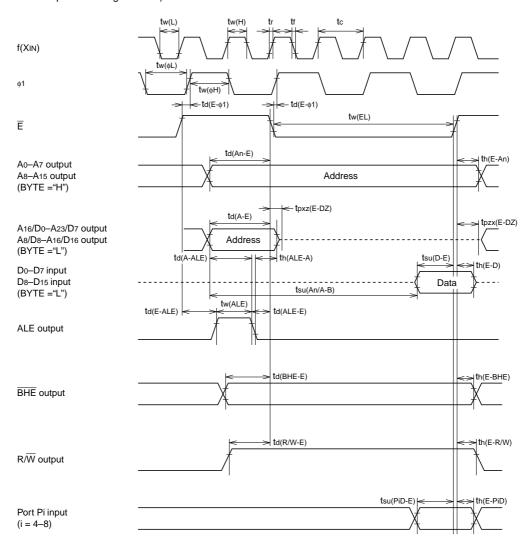
• Input timing voltage : VIL = 1.0 V, VIH = 4.0 V

• Output timing voltage : VOL = 0.8 V, VOH = 2.0 V, CL = 100 pF





(when $3-\phi$ access in low-speed running <Read>)



Test conditions (except Port Pi, f(XIN))

- VCC = 5 V±10 %
- \bullet Output timing voltage : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF
- Data input : VIL = 0.8 V, VIH = 2.5 V

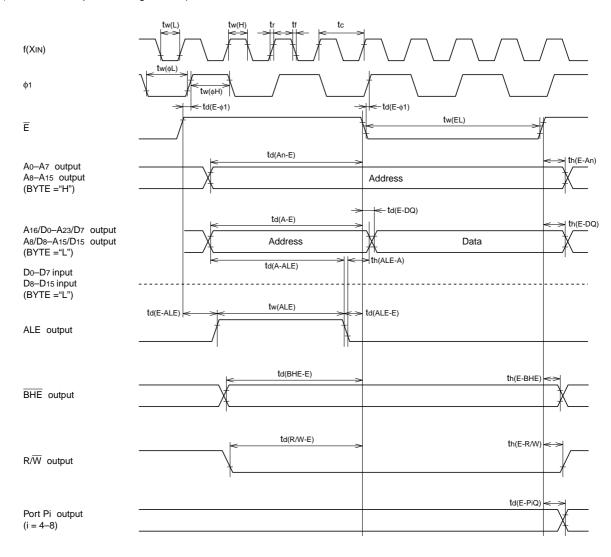
- Vcc = 5 V±10 %
- \bullet Input timing voltage : VIL = 1.0 V, VIH = 4.0 V
- Output timing voltage : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF







(when $4-\phi$ access in low-speed running <Write>)



Test conditions (except Port Pi, f(XIN))

- Vcc = 5 V±10 %
- Output timing voltage : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF Data input : VIL = 0.8 V, VIH = 2.5 V

Test conditions (Port Pi, f(XIN))
• VCC = 5 V±10 %

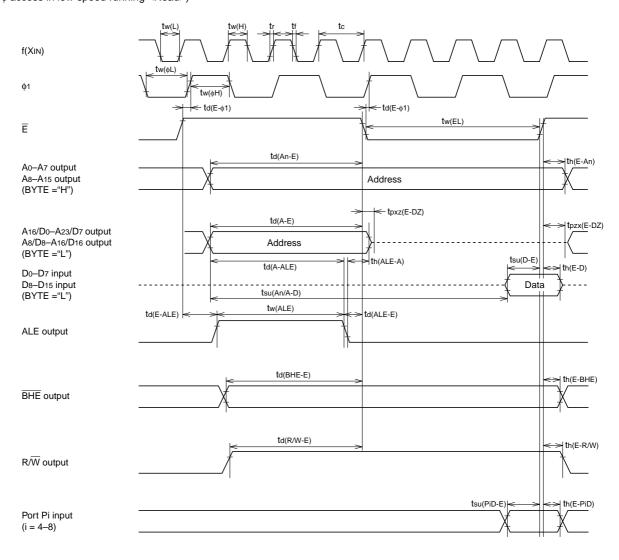
- Input timing voltage: VIL = 1.0 V, VIH = 4.0 V
 Output timing voltage: VoL = 0.8 V, VOH = 2.0 V, CL = 100 pF







(when $4-\phi$ access in low-speed running <Read>)



Test conditions (except Port Pi, f(XIN))

• Vcc = 5 V±10 %

• Output timing voltage : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF

• Data input : VIL = 0.8 V, VIH = 2.5 V

Test conditions (Port Pi, f(XIN))

• VCC = 5 V±10 %

• Input timing voltage : VIL = 1.0 V, VIH = 4.0 V

• Output timing voltage : VOL = 0.8 V, VOH = 2.0 V, CL = 100 pF





SHINGLE-CHIP 16-BIT CMOS MICROCOMPUTER FLASH MEMORY VERSION

Timing requirements (Vcc = 5 V±10 %, Vss = 0 V, Ta = -20 to 85 °C, f(XIN)=40 MHz when the clock source select bit = "0"*, unless otherwise noted)

* The rise and fall time of input signal must be 100 ns or less respectively, unless otherwise noted.

Memory expansion and Microprocessor mode: High-speed running

0	Demonstra	L	imits	11.2
Symbol	Parameter	Min.	Max.	Unit
tc	External clock input cycle time (Note 1)	25		ns
tw(H)	External clock input high-level pulse width (Note 2)	tc/2 - 8		ns
tw(L)	External clock input low-level pulse width (Note 2)	tc/2 - 8		ns
tr	External clock rise time		8	ns
tf	External clock fall time		8	ns
tsu(D-E)	Input setup time	30		ns
tsu(PiD-E)	Port Pi input setup time (i = 4—8)	60		ns
th(E-D)	Data input hold time	0		ns
th(E-PiD)	Port Pi input hold time (i = 4—8)	0		ns
			50 (3-φ access)	
tsu(An/A-D)	Data setup time with address stabilized (Note 3)		100 (4-φ access)	ns
			150 (5-φ access)	1

^{*:} f(XIN) = 20 MHz when the clock source selet bit = "1"

Notes 1: When the clock source select bit = "1", tc's minimum limit is 50 ns.

- 2: When the clock source select bit = "1", set tw(H)/tc and tw(L)/tc ratios to 45 to 55 %.
- **3:** Since the values depend on external clock input frequency f(XIN), calculate them using the bus timing data formula on the page after the next page.





SHINGLE-CHIP 16-BIT CMOS MICROCOMPUTER FLASH MEMORY VERSION

Switching characteristics (Vcc = $5 \text{ V} \pm 10 \text{ %}$, Vss = 0 V, Ta = -20 to 85 °C, f(XIN) = 40 MHz when the clock source select bit = "0"*, unless otherwise noted)

Memory expansion and Microprocessor mode: High-speed running

O make at	Description	Parameter 3 M		ccess	4-φ access		5-φ access		1.111
Symbol	Parameter			Max.	Min.	Max.	Min.	Max.	Unit
$tw(\phiH),\;tw(\phiL)$	ϕ high-level pulse width, ϕ low-level pulse width	(Note)	5		5		5		ns
td(E− <i>φ</i> 1)	ϕ 1 output delay time		-12	7	-12	7	-12	7	ns
tw(EL)	E low-level pulse width	(Note)	50		75		125		ns
td(An–E)	Address output delay time	(Note)	15		40		40		ns
td(E-DQ)	Data output delay time			35		35		35	ns
tpxz(E-DZ)	Floating start delay time			5		5		5	ns
td(A-E)	Address output delay time	(Note)	15		40		40		ns
td(A-ALE)	Address output delay time	(Note)	5		30		30		ns
td(E-ALE)	ALE output delay time	(Note)	10		10		10		ns
td(ALE-E)	ALE output delay time	(Note)	4		4		4		ns
tw(ALE)	ALE pulse width	(Note)	10		35		35		ns
td(BHE-E)	BHE output delay time	(Note)	20		45		45		ns
td(R/W-E)	R/W output delay time	(Note)	20		45		45		ns
th(E-An)	Address hold time	(Note)	10		10		10		ns
th(ALE-A)	Address hold time	(Note)	10		10		10		ns
th(E-DQ)	Data hold time	(Note)	15		15		15		ns
tPZX(E-DZ)	Floating release delay time	(Note)	15		15		15		ns
th(E-BHE)	BHE hold time	(Note)	10		10		10		ns
th(E-R/W)	R/W hold time	(Note)	10		10		10		ns
td(E-PiQ)	Port Pi data output delay time (i = 4–8)			60		60		60	ns

^{*}: f(XIN) = 20 MHz when the clock source selet bit = "1"

Note: Since the values depend on external clock frequency f(XIN), calculate them by using the bus timing data formulas on the next page.







Bus timing data formulas

Memory expansion and Microprocessor mode : High-speed running (VCC = 5 V \pm 10 %, VSS = 0 V, Ta = -20 to 85 °C, f(XIN) \leq 40 MHz when the clock source select bit = "0"*, unless otherwise noted)

Symbol	Parameter	3-φ access	4-φ access	5-φ access	Unit
tsu(An/A-D)	Data setup time with address stabilized	$\frac{5 \times 10^9}{f(XIN)} - 75$	$\frac{7\times10^9}{f(XIN)}-75$	$\frac{9 \times 10^9}{f(XIN)} - 75$	ns
tw(φH), tw(φL)	ϕ high-level pulse width, ϕ low-level pulse width	$\frac{1\times10^9}{f(XIN)}-20$	-	-	ns
tw(EL)	E low-level pulse width	$\frac{3 \times 10^9}{f(XIN)}$ -25	$\frac{4\times10^9}{f(XIN)}-25$	$\frac{6 \times 10^9}{f(XIN)}$ -25	ns
td(An-E)	Address output delay time	$\frac{2\times10^9}{f(XIN)}-35$	$\frac{3\times10^9}{f(XIN)}-35$	-	ns
td(A-E)	Address output delay time	$\frac{2 \times 10^9}{f(XIN)}$ -35	$\frac{3\times10^9}{f(XIN)}-35$	-	ns
td(A-ALE)	Address output delay time	$\frac{1\times10^9}{f(XIN)}$ -20	$\frac{2\times10^9}{f(XIN)}-20$	-	ns
td(E-ALE)	ALE outuput delay time	$\frac{1\times10^9}{f(XIN)}$ -15	-	-	ns
tw(ALE)	ALE pulse width	$\frac{1 \times 10^9}{f(XIN)} - 15$	$\frac{2 \times 10^9}{f(XIN)}$ -15	-	ns
td(BHE-E)	BHE outuput delay time	$\frac{2 \times 10^9}{f(XIN)}$ -30	$\frac{3\times10^9}{f(XIN)}-30$	-	ns
td(R/W-E)	RM outuput delay time	$\frac{2\times10^9}{f(XIN)}$ -30	$\frac{3\times10^9}{f(XIN)}-30$	-	ns
th(E-An)	Address hold time	$\frac{1 \times 10^9}{f(XIN)} - 15$	-	-	ns
th(ALE-A)	Address hold time	$\frac{1 \times 10^9}{f(XIN)}$ -15	-	-	ns
th(E-DQ)	Data hold time	$\frac{1 \times 10^9}{f(XIN)} - 10$	-	-	ns
tpzx(E-DZ)	Floating release delay time	$\frac{1\times10^9}{f(XIN)}-10$	-	-	ns
td(E-BHE)	BHE hold time	$\frac{1 \times 10^9}{f(XIN)}$ -15	-	-	ns
td(E-R/W)	R/W hold time	$\frac{1 \times 10^9}{f(XIN)} - 15$	-	-	ns

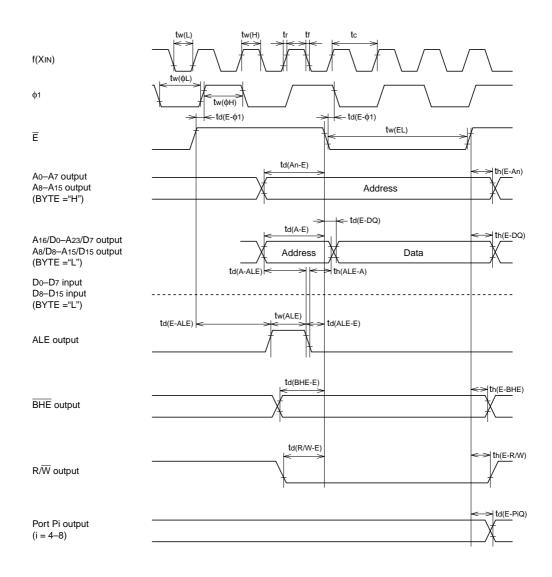
*: $f(XIN) \le 20$ MHz when the clock source select bit = "1"

Note: When the clock source select bit is "1", regard f(XIN) in tables as 2-f(XIN).





(when $3-\phi$ access in high-speed running <Write>)



Test conditions (except Port Pi, f(XIN))

- Vcc = 5 V±10 %
- \bullet Output timing voltage : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF
- Data input : VIL = 0.8 V, VIH = 2.5 V

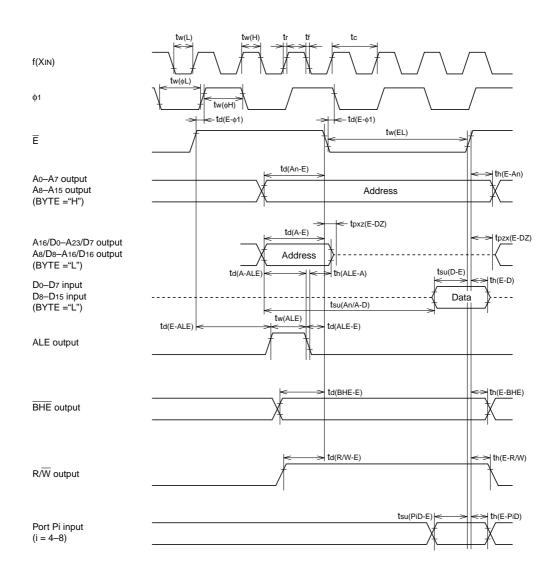
- Vcc = 5 V±10 %
- \bullet Input timing voltage : VIL = 1.0 V, VIH = 4.0 V
- Output timing voltage: VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF







(when $3-\phi$ access in high-speed running <Read>)



Test conditions (except Port Pi, f(XIN))

- VCC = 5 V±10 %
- Output timing voltage: Vol = 0.8 V, Voh = 2.0 V, Cl = 100 pF
 Data input: VIL = 0.8 V, VIH = 2.5 V

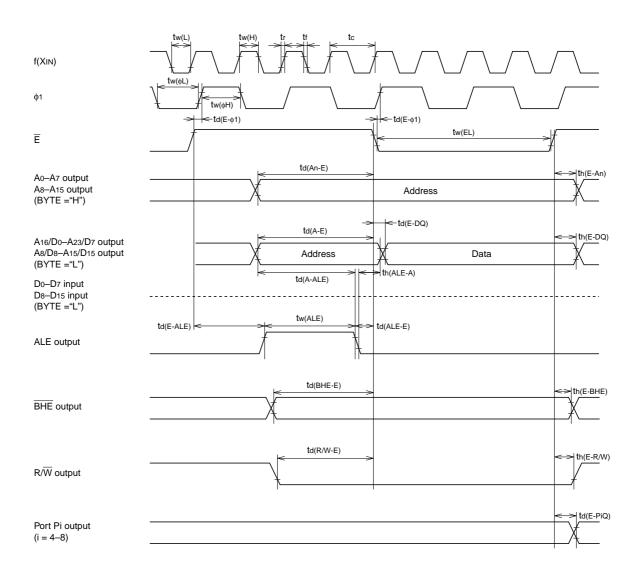
- Vcc = 5 V±10 %
- Input timing voltage: VIL = 1.0 V, VIH = 4.0 V
 Output timing voltage: VOL = 0.8 V, VOH = 2.0 V, CL = 100 pF







(when $4-\phi$ access in high-speed running <Write>)



Test conditions (except Port Pi, f(XIN))

- Vcc = 5 V±10 %
- Output timing voltage : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF Data input : VIL = 0.8 V, VIH = 2.5 V

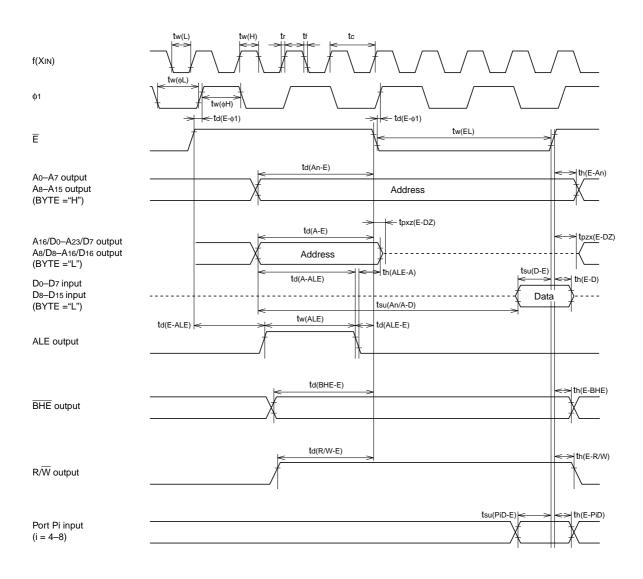
- Vcc = 5 V±10 %
- Input timing voltage : VIL = 1.0 V, VIH = 4.0 V
- Output timing voltage : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF







(when $4-\phi$ access in high-speed running <Read>)



Test conditions (except Port Pi, f(XIN))

- Vcc = 5 V±10 %
- \bullet Output timing voltage : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF
- Data input : VIL = 0.8 V, VIH = 2.5 V

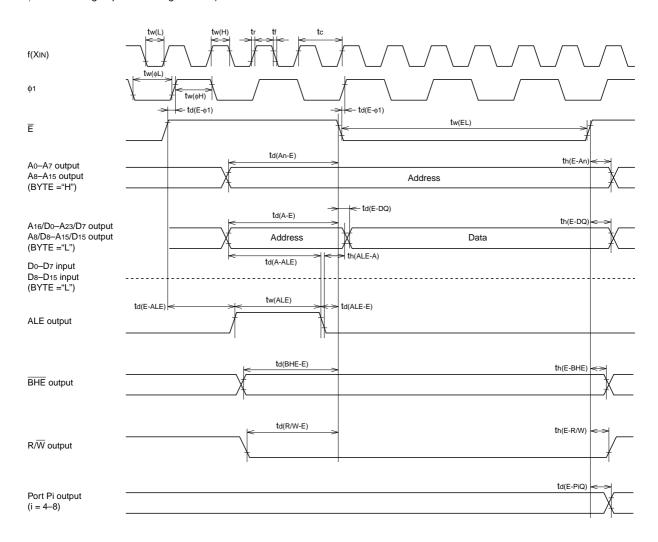
- VCC = 5 V±10 %
- \bullet Input timing voltage : VIL = 1.0 V, VIH = 4.0 V
- \bullet Output timing voltage : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF







(when 5- ϕ access in high-speed running <Write>)



Test conditions (except Port Pi, f(XIN))

• Vcc = 5 V±10 %

Output timing voltage: VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF
Data input: VIL = 0.8 V, VIH = 2.5 V

Test conditions (Port Pi, f(XIN))

• Input timing voltage : VIL = 1.0 V, VIH = 4.0 V

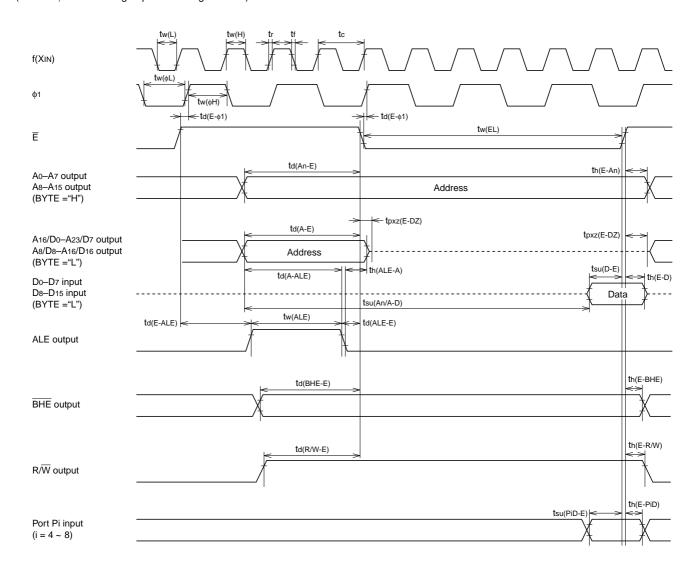
• Output timing voltage : VOL = 0.8 V, VOH = 2.0 V, CL = 100 pF







(when 5- ϕ access in high-speed running <Read>)



Test conditions (except Port Pi, f(XIN))

- Vcc = 5 V±10 %
- Output timing voltage : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF Data input : VIL = 0.8 V, VIH = 2.5 V

- Vcc = 5 V±10 %
- Input timing voltage: VIL = 1.0 V, VIH = 4.0 V
- Output timing voltage: VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF







<NOTE> External bus timing when internal memory area is accessed (2- ϕ access) in high-speed running

 $(VCC = 5 V \pm 10 \%, VSS = 0 V, Ta = -20 \text{ to } 85 ^{\circ}C, f(XIN) \le 40 \text{ MHz}$ when the clock source select bit = "0"*)

Symbol	%, VSS = 0 V, T_a = -20 to 85 °C, $f(XIN) \le 40$ MHz when the clock source select Parameter	Limits		Bus timing	1.1:4
		Min.	Max.	data formula	Unit
tw(φH), tw(φL)	ϕ high-level pulse width, ϕ low-level pulse width	5		$\frac{1\times10^9}{f(XIN)}-20$	ns
td(E-φ1)	ϕ 1 output delay time	-12	7		ns
tw(EL)	E low-level pulse width	5		$\frac{1\times10^9}{f(XIN)}-20$	ns
td(An–E)	Address output delay time	15		$\frac{2\times10^9}{f(XIN)}-35$	ns
tpxz(E–DZ)	Floating start delay time (BYTE="L")		5		ns
td(A–E)	Address output delay time	15		$\frac{2\times10^9}{f(XIN)}-35$	ns
td(A-ALE)	Address output delay time	5		$\frac{1\times10^9}{f(XIN)}-20$	ns
td(E-ALE)	ALE output delay time	10		$\frac{1\times10^9}{f(XIN)}-15$	ns
td(ALE-E)	ALE output delay time	4			ns
tw(ALE)	ALE pulse width	10		$\frac{1\times10^9}{f(XIN)}-15$	ns
td(BHE-E)	BHE output delay time	20		$\frac{2\times10^9}{f(XIN)}-30$	ns
td(R/W-E)	R/W output delay time	20		$\frac{2\times10^9}{f(XIN)}-30$	ns
th(E-An)	Address hold time	10		$\frac{1\times10^9}{f(XIN)}-15$	ns
th(ALE-A)	Address hold time (BYTE="L")	10		$\frac{1\times10^9}{f(XIN)}-15$	ns
tpzx(E–DZ)	Floating release delay time (BYTE="L")	15		$\frac{1\times10^9}{f(XIN)}-10$	ns
td(E-BHE)	BHE hold time	10		$\frac{1\times10^9}{f(XIN)}-15$	ns
td(E-R/W)	R/W hold time	10		$\frac{1\times10^9}{f(XIN)}-15$	ns

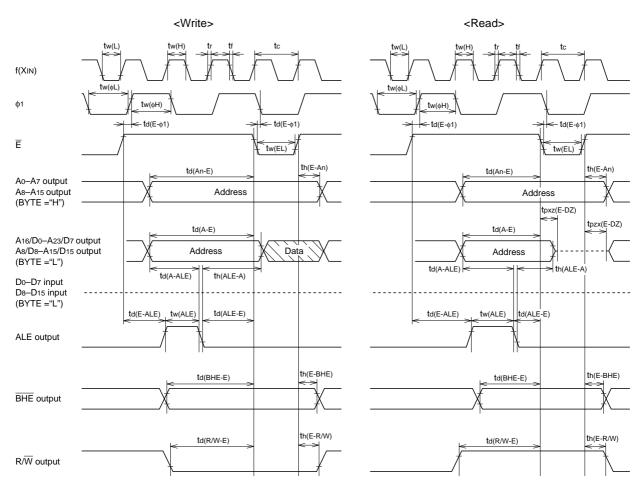
^{*:} $f(XIN) \le 20$ MHz when the clock source select bit = "1".







(External bus timing on internal RAM access (2-φ access) in high-speed running)



^{*} The value of write data is undefined.

Test conditions

Contents of external data bus cannot be read into the internal.

[•] Vcc = 5 V±10 %

 $[\]bullet$ Output timing voltage : VoL = 0.8 V, VoH = 2.0 V, CL = 100 pF

Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

- These materials are intended as a reference to assist our customers in the selection of the Mitsubishi semiconductor product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Mitsubishi Electric Corporation or a third party.

 Mitsubishi Electric Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts or circuit application examples contained in these materials.

 These materials are intended as a reference to assist our customers in the selection of the Mitsubishi Electric Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts or circuit application examples contained in these materials.
- All information contained in these materials, including product data, diagrams and charts, represent information on products at the time of publication of these materials, and are subject to change by Mitsubishi
- Electric Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor for the latest product information before purchasing a product listed herein.

 Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor growth at a device or system that is used under circumstances in which human life is potentially at stake. Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.

 The prior written approval of Mitsubishi Electric Corporation is necessary to reprint or reproduce in whole or in part these materials.

 If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the

- approved destination.

 Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.

 Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor for further details on these materials or the products contained therein.



Rev. No.	Revision Description	Rev. date
1.0	First Edition	971031